



EP 1 291 954 A2

(43) Date of publication:
12.03.2003 Bulletin 2003/11

(51) Int Cl.⁷: **H01P 1/15**, H01P 1/203,
H01P 1/213

(21) Application number: 02019050.0

(22) Date of filing: 27.08.2002

(84) Designated Contracting States:
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR
IE IT LI LU MC NL PT SE SK TR
Designated Extension States:
AL LT LV MK RO SI

(30) Priority: 27.08.2001 JP 2001255685

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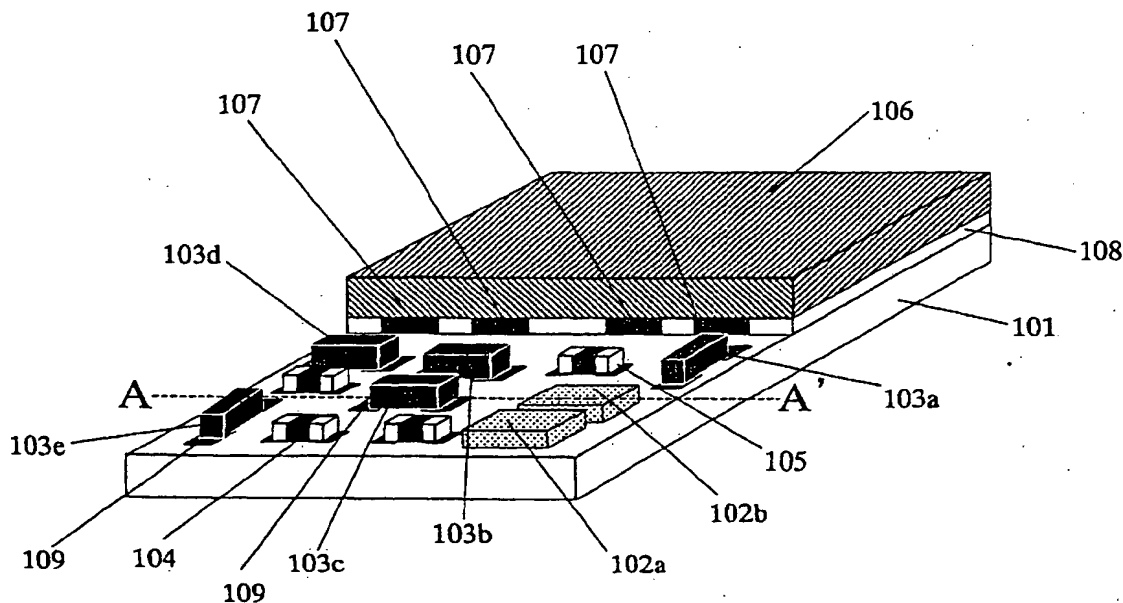
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(54) RF device and communication apparatus using the same

(57) An RF device, has a first substrate made of a material with a lower relative dielectric constant and having a high frequency circuit formed therein or on a surface thereof; and
a second substrate made of a material with a high-

er relative dielectric constant,
wherein at least a part of a filter is provided in, on
a surface of or in the vicinity of the second substrate and
connected to the high frequency circuit, and
the high frequency circuit is composed of an ele-
ment other than the part of the filter.

Fig. 1



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Description

BACKGROUND OF THE INVENTION

5 Field of the Invention

[0001] The present invention relates to an RF device mainly used in a high frequency radio apparatus, such as a cellular phone.

10 Related Art of the Invention

[0002] Recently, as mobile communication users have been increased and a system therefor has become global, an RF device has become a focus of attention that enables the EGSM, DCS and UMTS systems provided for respective frequencies shown in FIG. 18 to be used with one cellular phone. With reference to drawings, a first conventional RF device will be described below.

[0003] FIG. 19 is a cross-sectional view of the first conventional RF device. In FIG. 19, reference numeral 1101 denotes a low temperature cofired ceramic body with a low relative dielectric constant. Reference numeral 1102 denotes a multilayered wiring conductor for constituting part of an RF circuit. Reference numeral 1103 denotes an interlayer via hole and reference numeral 1104 denotes a discrete component, such as a discrete resistor, a discrete capacitor, a discrete inductor and a packaged semiconductor.

[0004] FIG. 20 is a circuit diagram of the first conventional RF device. The RF device is one provided for triple bands (EGSM, DCS and UMTS described above) comprising a diplexer 1201 that connects a transmitting/receiving switching circuit 1202 and a transmitting/receiving switching circuit 1203 to an antenna (ANT).

[0005] An operation of the first conventional RF device arranged as described above will be described.

[0006] The multilayered wiring conductor 1102 electrically interconnects a plurality of discrete components 1104 and, in a substrate 1101 made of a low temperature cofired ceramic, forms a capacitor formed in the substrate and an inductor formed in the substrate. Such capacitor and inductor constitute an RF circuit in conjunction with the discrete components 1104, and the RF circuit serves as an RF device such as an RF multilayered switch.

[0007] The diplexer 1201 directly connected to the antenna terminal (ANT) branches a signal received through the antenna terminal (ANT) to the transmitting/receiving switching circuits 1202 and 1203. The diplexer 1204 is connected to the transmitting/receiving switching circuit 1203. The transmitting/receiving switching circuit 1202 has a transmitting terminal Tx1 for EGSM transmitting and a receiving terminal Rx1 for EGSM receiving. The transmitting/receiving switching circuit 1203 has a transmitting terminal Tx2 for DCS transmitting and a receiving terminal Rx2 for DCS receiving. The diplexer 1204 has a transmitting terminal Tx3 for UMTS transmitting and a receiving terminal Rx3 for UMTS receiving.

[0008] The receiving terminal Rx2 is connected to the antenna via a diode 1205, which is in the off state during transmission using the transmitting terminal Tx2.

[0009] Transmission line 1206a and 1206b for electrical length correction, a transmitting filter 1207 and a receiving filter 1208, which are required for duplex transmission, are connected between the transmitting terminal Tx3 and the receiving terminal Rx3.

[0010] Now, a second conventional RF device will be described as another example of the send/receive switching circuit directly connected to the antenna.

[0011] FIG. 21 is an exploded perspective view of the second conventional RF device. The RF device has six dielectric substrates with high relative dielectric constant 1301a to 1301f. The dielectric substrate 1301b having a shielding electrode 1302a formed on the upper surface thereof, the dielectric substrate 1301c having an inter-stage coupling electrode 1303 formed on the upper surface thereof, the dielectric substrate 1301d having resonator electrodes 1304a and 1304b formed on the upper surface thereof, the dielectric substrate 1301e having input/output coupling capacitor electrodes 1305a and 1305b formed on the upper surface thereof, and the dielectric substrate 1301f having a shielding electrode 1302b formed on the upper surface thereof are stacked.

[0012] End face electrodes 1306a and 1306b, which are connected to the shielding electrodes 1302a and 1302b to form ground terminals, are provided at the left and right sides of the stacked dielectric substrates. On the rear of the stacked dielectric substrates, there is provided an end face electrode 1307 which is connected to the ground facing the shielding electrodes 1302a and 1302b and a common open end of the microstrip resonator electrodes 1304a and 1304b. An end face electrode 1308, which is provided on the front of the stacked dielectric substrates, is connected to short-circuit ends of the resonator electrodes 1304a and 1304b and to the shielding electrodes 1302a and 1302b. End face electrodes 1309a and 1309b at the left and right sides of the stacked dielectric substrates are connected to the input/output coupling electrodes 1305a and 1305b to constitute input/output terminals.

[0013] FIG. 22 is a circuit diagram of the second conventional RF device. The input/output coupling electrode 1305a

and the resonator electrode 1304a constitute an input/output coupling capacitor 1401a, and the input/output coupling electrode 1305b and the resonator electrode 1304b constitute an input/output coupling capacitor 1401b. In addition, the input/output coupling electrode 1305a and the inter-stage coupling electrode 1303 constitute an inter-stage coupling capacitor 1402a, and the input/output coupling electrode 1305b and the inter-stage coupling electrode 1303 constitute an inter-stage coupling capacitor 1402b. These components constitute a two-stage band-pass filter shown in FIG. 22.

[0014] FIG. 23 is a block diagram of an antenna duplexer 1503, which is the second conventional RF device, comprising a transmitting filter 1501, a receiving filter 1502, the filters being constituted by the band-pass filter, and a matching circuit provided therebetween.

[0015] However, the first conventional RF device configured as described above, the transmitting filter 1206 and the receiving filter 1027 are composed of an inductor or capacitor with a low Quality factor, and therefore, have a high loss as a filter. Furthermore, the microstrip resonator structure for increasing the Quality factor has a problem in that the RF device including the substrate 1101 made of a low temperature cofired ceramic with low relative dielectric constant becomes quite large because the size of the resonator is inversely proportional to the frequency and the square root of the relative dielectric constant.

[0016] Even with the microstrip resonator structure, since it is also affected by the substrate 1101 with low relative dielectric constant, the Quality factor cannot be increased sufficiently, and for example, a circuit provided for the CDMA mode still has a problem of the filter loss.

[0017] In the second conventional RF device configured as described above, if a line is provided thereon or therein, the impedance of the line is increased because the substrates constituting the RF multilayered device are made of a low temperature cofired ceramic with high relative dielectric constant, and thus, it is quite difficult to form a complicated circuit in each substrate. In addition, it is also quite difficult to implement a discrete component, such as a discrete resistor, a discrete capacitor, a discrete inductor and a packaged semiconductor, on the second conventional RF device, because the line impedance of the discrete component itself is increased.

SUMMARY OF THE INVENTION

[0018] In view of the above described problems, an object of this invention is to provide an RF device having a low filter loss and not suffering from a problem about a line impedance, or a compact RF device not suffering from a problem about a line impedance.

[0019] The 1st invention of the present invention is an RF device, comprising:

- a first substrate made of a material with a lower relative dielectric constant and having a high frequency circuit formed therein or on a surface thereof; and
- a second substrate made of a material with a higher relative dielectric constant,

wherein at least a part of a filter is provided in, on a surface of or in the vicinity of said second substrate and connected to said high frequency circuit, and

said high frequency circuit is composed of an element other than said part of the filter.

[0020] The 2nd invention of the present invention is the RF device according to 1st invention, wherein said at least a part of the filter forms a high frequency circuit for a CDMA mode.

[0021] The 3rd invention of the present invention is the RF device according to 1st invention, wherein said second substrate is partially overlaid on said first substrate, a semiconductor device or passive device is provided on a region in the surface of said first substrate on which said second substrate is not overlaid, and a multilayered wiring pattern made of copper or silver is formed in said first substrate, whereby said high frequency circuit is formed.

[0022] The 4th invention of the present invention is the RF device according to 3rd invention, wherein said semiconductor device includes any one of a PIN diode device, a GaAs semiconductor device, a field effect transistor (FET) device and a varactor diode device, and switching among a plurality of frequency bands is realized by an operation of any one of said devices.

[0023] The 5th invention of the present invention is an RF device, comprising:

- a first substrate made of a material with a lower relative dielectric constant and having a first high frequency circuit for a lower frequency band formed therein or on a surface thereof; and
- a second substrate made of a material with a higher relative dielectric constant,

wherein at least a part of a filter of a second high frequency circuit for a higher frequency band is provided in, on a surface of or in the vicinity of said second substrate, and said first high frequency circuit and said second high frequency circuit are connected to each other.

[0024] The 6th invention of the present invention is the RF device according to 5th invention, wherein said second

substrate is overlaid on said first substrate, and said part of the filter is sandwiched between said first substrate and said second substrate.

[0025] The 7th invention of the present invention is the RF device according to 6th invention, wherein said second substrate is partially overlaid on said first substrate, a semiconductor device or passive device is provided on a region in the surface of said first substrate on which said second substrate is not overlaid, and a multilayered wiring pattern made of copper or silver is formed in said first substrate, whereby said first high frequency circuit is formed.

[0026] The 8th invention of the present invention is the RF device according to 7th invention, wherein said second substrate comprises a plurality of substrates disposed on said first substrate with spaced apart from each other, one of said plurality of substrates constitutes a transmitting filter, and another of said plurality of substrates constitutes a receiving filter.

[0027] The 9th invention of the present invention is the RF device according to 5th invention, wherein said lower frequency band is a frequency band for a TDMA mode, and said higher frequency band is a frequency band for a CDMA mode.

[0028] The 10th invention of the present invention is the RF device according to 5th invention, wherein each of said first and second substrates is composed of a multilayered and integrally molded ceramic.

[0029] The 11th invention of the present invention is the RF device according to 5th invention, wherein said first substrate is made of a low temperature cofired ceramic and said second substrate is made of a high temperature cofired ceramic.

[0030] The 12th invention of the present invention is the RF device according to 6th invention, wherein a part of said filter is a resonator electrode, and said resonator electrode is constituted by a metal foil.

[0031] The 13th invention of the present invention is the RF device according to 12th invention, wherein the RF device is integrated by filling a space defined by said first substrate, said second substrate and said resonator electrode with a thermosetting resin.

[0032] The 14th invention of the present invention is the RF device according to 7th invention, wherein said semiconductor device includes any one of a PIN diode device, a GaAs semiconductor device, a field effect transistor (FET) device and a varactor diode device, and switching between said first high frequency circuit and said second high frequency circuit is realized by an operation of any one of said devices.

[0033] The 15th invention of the present invention is the RF device according to 5th invention, wherein whole or a part of said second substrate is covered with a shielding electrode.

[0034] The 16th invention of the present invention is the RF device according to 7th invention, wherein said passive device includes a SAW filter with an electrode hermetically sealed.

[0035] The 17th invention of the present invention is a communication apparatus, comprising the RF device according to any one of 1st to 16th inventions, a transmitting circuit, a receiving circuit and an antenna which are connected to said RF device.

BRIEF DESCRIPTION OF THE DRAWINGS

[0036] FIG. 1 is a perspective view of an RF device according to an embodiment 1 of this invention.

[0037] FIG. 2 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0038] FIG. 3 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0039] FIG. 4 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0040] FIG. 5 is a cross-sectional view of the RF device taken along a line A-A' in FIG. 1.

[0041] FIG. 6 is a block diagram of the RF device according to the embodiment 1 of this invention.

[0042] FIG. 7 is an equivalent circuit diagram of the RF device according to the embodiment 1 of this invention.

[0043] FIG. 8 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0044] FIG. 9 is an equivalent circuit diagram of the RF device according to an embodiment 2 of this invention.

[0045] FIG. 10 illustrates a switch circuit, including a PIN diode, of the RF device according to the embodiment 2 of this invention.

[0046] FIG. 11 is a partial perspective view of the RF device according to the embodiment 2 of this invention.

[0047] FIG. 12 is a graph showing a transfer characteristic of the RF device according to the embodiment 2 of this invention.

[0048] FIG. 13 shows a configuration of the RF device including a FET according to the embodiment 2 of this invention.

[0049] FIG. 14 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0050] FIG. 15 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0051] FIG. 16 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0052] FIG. 17 is a perspective view of the RF device according to the embodiment 1 of this invention.

[0053] FIG. 18 shows frequencies of a plurality of systems for which a first conventional RF device operates.

- [0054] FIG. 19 is a cross-sectional view of the first conventional RF device.
 [0055] FIG. 20 is a circuit diagram of the first conventional RF device.
 [0056] FIG. 21 is an exploded perspective view of a second conventional RF device.
 [0057] FIG. 22 is a circuit diagram of the second conventional RF device.
 5 [0058] FIG. 23 is a block diagram of a duplexer of the second conventional RF device.

Description of Symbols

[0059]

10	101	Low temperature cofired ceramic with low dielectric constant
	102a,	102b SAW filter
	103a,	103b, 103c, 103d, 103e PIN diode
	104	Discrete inductor
15	105	Discrete capacitor
	106	Ceramic with high dielectric constant
	107	Metal foil resonator
	108	Thermosetting resin
	109	Upper external electrode
20	201	Multilayered wiring conductor
	202	Interlayer via hole
	203	Bottom surface terminal electrode (LGA)
	301,	302 Switch circuit
	303	Diplexer
25	304,	305 Internal terminal
	306	Antenna terminal
	307a,	307b LPF
	308	Duplexer
	401	Control terminal
30	402	Resistor
	403	Control terminal
	404	Resistor
	405	Control terminal
	406	Resistor
35	407	Transmitting filter
	408	Receiving filter
	409	Transmission line
	410	Transmission line
	411a, 411b	Quarter-wavelength tip-short-circuited resonator
40	412	Inter-stage coupling capacitor
	413a, 413b	Input/output coupling capacitor
	414a, 414b	Quarter-wavelength tip-short-circuited resonator
	415	Inter-stage coupling capacitor
	416a, 416b	Input/output coupling capacitor
45	501, 505	Resonator
	506, 507	Series capacitor
	508, 509	Ground capacitor
	510, 512	Coupling inductor
	513, 514	Coupling capacitor
50	515, 516	Bypass capacitor
	517	Capacitor for matching between terminals
	518	Inductor for matching between terminals
	519, 520, 521, 522, 523	Switch
	524, 525, 526, 527, 528	Switch coupling capacitor
55	529	Antenna terminal
	530	Transmitting terminal
	531	Receiving terminal
	601	PIN diode

602	Coupling capacitor
603	Choke coil
604	Bypass capacitor
605	Resistor
5 606	Control terminal
701	Metal foil resonator
702	Low temperature cofired ceramic with low dielectric constant
703	Ceramic with high dielectric constant
704	Thermosetting resin
10 901	Field effect transistor (FET)
902	Bypass capacitor
903	Control terminal
1101	Low temperature cofired ceramic body with low dielectric constant
1102	Multilayered wiring conductor
15 1103	Interlayer via hole
1104	Discrete component
1201	Diplexer
1202	Send/receive switching circuit
1203	Send/receive switching circuit
20 1204	Duplexer
1205	Diode
1206a, 1206b	Transmission line
1207	Transmitting filter
1208	Receiving filter
25 1301a, 1301e	Dielectric substrate with high dielectric constant
1302a, 1302b	Shielding electrode
1303	Inter-stage coupling electrode
1304a, 1304b	Microstrip resonator electrode
1305a, 1305b	Input/output coupling electrode
30 1306a, 1306b	End face electrode
1307	End face electrode
1308	End face electrode
1309a, 1309b	Input/output terminal
1401a, 1401e	Input/output coupling capacitor
35 1402a, 1402b	Inter-stage coupling capacitor

PREFERRED EMBODIMENTS OF THE INVENTION

[0060] Now, an RF device according to this invention will be described with reference to the drawings.

(Embodiment 1)

[0061] FIG. 1 is a perspective view of an RF device according to an embodiment 1 of this invention. A substrate 101 is an example of a first substrate according to this invention, which is made of a low temperature cofired ceramic with low dielectric constant (hereinafter, "low dielectric constant" means a lower relative dielectric constant). Reference numerals 102a and 102b denote a SAW filter, reference numerals 103a to 103e denote a PIN diode, which is one example of a semiconductor device according to this invention, reference numeral 104 denotes a discrete inductor, reference numeral 105 denotes a discrete capacitor, and a substrate 106 is an example of a second substrate according to this invention, which is made of a high temperature cofired ceramic with high dielectric constant (hereinafter, "high dielectric constant" means a higher relative dielectric constant). A metal foil resonator 107 is one example of a part of a resonator according to this invention. Reference numeral 108 denotes a thermosetting resin and reference numeral 109 denotes an upper surface external electrode.

[0062] FIG. 5 is a cross-sectional view of the RF device shown in FIG. 1 taken along a line A-A'. Reference numeral 201 denotes a multilayered wiring conductor, reference numeral 202 denotes an interlayer via hole, and reference numeral 203 denotes a bottom surface terminal electrode (LGA: Land Grid Array).

[0063] FIG. 6 is a block diagram of the RF device according to the embodiment 1 of this invention. Reference numerals 301 and 302 denote a switching circuit (send/receive switching circuit). Reference numeral 303 denotes a diplexer, and specifically, reference numeral 303a denotes a low pass filter (LPF) and reference numeral 303b denotes a high

pass filter (HPF). Reference numerals 304 and 305 denote an internal terminal, reference numeral 306 denotes an antenna terminal, reference numerals 307a and 307b denote an LPF, and reference numeral 308 denotes a duplexer (Dup).

[0064] FIG. 7 is an equivalent circuit diagram of the RF device according to the embodiment 1 of this invention. Reference numeral 401 denotes a control terminal, reference numeral 402 denotes a resistor, reference numeral 403 denotes a control terminal, reference numeral 404 denotes a resistor, reference numeral 405 denotes a control terminal, reference numeral 406 denotes a resistor, reference numeral 407 denotes a transmitting filter, reference numeral 408 denotes a receiving filter, reference numerals 409 and 410 denote a transmission line, reference numerals 411a and 411b denote a quarter-wavelength tip-short-circuited resonator, reference numeral 412 denotes an inter-stage coupling capacitor, reference numerals 413a and 413b denote an input/output coupling capacitor, reference numeral 414a and 414b denote a quarter-wavelength tip-short-circuited resonator, reference numeral 415 denotes an inter-stage coupling capacitor, and reference numerals 416a and 416b denote an input/output coupling capacitor.

[0065] In the substrate 101 made of a low temperature cofired ceramic with low dielectric constant, the multilayered wiring conductor 201 made of copper or silver, which is one example of the multilayered wiring pattern according to this invention, forms strip lines including the transmission lines 409, 410 with an impedance determined by thickness, width and length of the multilayered wiring conductor 201 and the dielectric constant of the substrate 101. In addition, the multilayered wiring conductors 201 disposed in different two layers form a capacitor in the substrate 101, the capacitor having an impedance determined by an overlapping area of the multilayered wiring conductors 201, the dielectric constant of the low temperature cofired ceramic with low dielectric constant sandwiched between the multilayered wiring conductors 201 or the like.

[0066] Since the substrate 101 made of the low temperature cofired ceramic with low dielectric constant is interposed between the multilayered wiring conductors 201 and the metal foil resonators 107, capacitors including the inter-stage coupling capacitors 412, 415 and the input/output coupling capacitors 413a, 413b, 416a and 416b are formed. In addition, in the substrate 101, the multilayered wiring conductor 201 forms an inductor having an impedance determined by width and length of the line of the multilayered wiring conductor 201 and the dielectric constant of the low temperature cofired ceramic with low dielectric constant.

[0067] The multilayered wiring conductors 201 are electrically connected to each other via the interlayer via hole 202 formed at a desired position between the multilayered wiring conductors 201. A pattern of the multilayered wiring conductor 201 in each layer is formed by screen printing or another method. The interlayer via hole 202 is formed by punching a hole in the dielectric sheet constituting the substrate 101 and filling the hole with a conductive paste by printing or another method. External connection terminals including the antenna terminal 306, transmitting terminals Tx1, Tx2 and Tx3, receiving terminals Rx1, Rx2 and Rx3 and control terminals 401, 403 and 405 are formed in the form of the bottom surface terminal electrode 203 disposed on the bottom surface of the substrate 101 via the strip line, the interlayer via hole 202 or the like.

[0068] On the upper surface of the substrate 101 made of the low temperature cofired ceramic with low dielectric constant, the substrate 106, which is one example of the second substrate according to this invention, made of a high temperature cofired ceramic with high dielectric constant and having a smaller area than the substrate 101 is disposed. Between the substrates 101 and 106, there is sandwiched a plurality of metal foil resonators 107 mainly made of gold, silver or copper, each of which is one example of a resonator electrode which is a part of the resonator according to this invention. Spaces between the metal foil resonators 107 are filled with the thermosetting resin 108, whereby the substrates 101 and 106 are interconnected and integrated.

[0069] The electrode 109, which is drawn to the upper surface of the substrate 101 via the interlayer via hole 202, is formed on the upper surface of the substrate 101 in a region where the metal foil resonator 107 and the substrate 106 are not formed. Devices which are difficult to form in the substrate 101, such as the two SAW filters 102, the five PIN diodes 103 and the discrete components including the discrete inductor 104 and the discrete capacitor 105, are mounted and electrically connected to the internal circuit in the stack assembly via the respective upper surface external electrodes 109 formed on the upper surface of the stack assembly.

[0070] As described above, in the circuit shown in FIG. 7, the duplexer 308 is shown as an example of a second high frequency circuit according to this invention, and the part other than the duplexer 308 is shown as an example of a first high frequency circuit according to this invention.

[0071] FIG. 8 shows an arrangement of electrodes 1413a, 1413b, 1416a, 1416b, 1412 and 1415, each of which constitutes a part of the input/output coupling capacitors 413a, 413b, 416a and 416b and inter-stage coupling capacitors 412 and 415, when forming the transmitting filter 407 and the receiving filter 408 from the substrate 106, the metal foil resonator 107 and the multilayered wiring conductor in the substrate 101.

[0072] Now, a circuit configuration of the RF device according to the embodiment 1 of this invention will be described.

[0073] The RF device according to the embodiment 1 of this invention is an RF device provided for triple bands having a filtering capability of passing therethrough transmitting frequency bands and receiving frequency bands of a first frequency band (EGSM), a second frequency band (DCS) and a third frequency band (UMTS), the first and second

frequency bands being examples of a lower frequency band of this invention, and the third frequency band being an example of a higher frequency band of this invention. The RF device comprises the switch circuits (send/receive switching circuits) 301 and 302 and the duplexer 303.

[0074] The duplexer 303 has the LPF 303a that is connected between the internal terminal 304 and the antenna terminal 306 to be connected to the antenna (ANT) and passes therethrough the first frequency band (EGSM), and the HPF 303b that is connected between the internal terminal 305 and the antenna terminal 306 and passes there- through the second frequency band (EGSM) and the third frequency band (UMTS).

[0075] The switch circuit 301 is switching means that is connected to the internal terminal 304 and switches between the transmitting terminal Tx1 and receiving terminal Rx1 for the first frequency band (EGSM) branched by the LPF 303a under the control of the control terminal 401. The LPF 307a for reducing a harmonic distortion caused by ampli- fication when transmitting via the transmitting terminal Tx1 is inserted between the switch circuit 301 and the transmitting terminal Tx1. In addition, the SAW filter 102a for reducing an undesired frequency component of a signal inputted through the antenna ANT when receiving via the receiving terminal Rx1 is inserted between the switch circuit 301 and the receiving terminal Rx1.

[0076] The switch circuit 302 is switching means that is connected to the internal terminal 305 and switches among the transmitting terminal Tx2 and receiving terminal Rx2 for the second frequency band (DCS) branched by the HPF 303b and the duplexer 308 for the third frequency band (UMTS) under the control of the control terminals 403 and 405. The low pass filter (LPF) 307b for reducing a harmonic distortion caused by amplification when transmitting via the transmitting terminal Tx2 is inserted between the switch circuit 302 and the transmitting terminal Tx2. In addition, the SAW filter 102b for reducing an undesired frequency component of a signal inputted through the antenna ANT when receiving via the receiving terminal Rx2 is inserted between the switch circuit 302 and the receiving terminal Rx2. The duplexer 308 is means of branching a signal in the third frequency band (UMTS) received via the switch circuit 302 to the transmitting terminal Tx3 and receiving terminal Rx3 for the third frequency band (UMTS).

[0077] A communication mode for the first frequency band (EGSM) and the second frequency band (DCS) is the TDMA (Time Division Multiple Access) mode. One example of the lower frequency band according to this invention is a frequency band for the TDMA mode. In this case, switching between the transmitting terminals Tx1, Tx2 and the receiving terminals Rx1, Rx2 is accomplished by means of an external diode. A communication mode for the third frequency band (UMTS) is the CDMA (Code Division Multiple Access) mode. One example of the higher frequency band according to this invention is a frequency band for the CDMA mode. The transmitting terminal Tx3 and the re- ceiving terminal Rx3 are provided via the duplexer 308.

[0078] The duplexer 308 is composed of the transmitting filter 407, the receiving filter 408 and the transmission lines 409, 410 having an optimum electrical length and connected to the filters. For example, the transmitting filter 407 is a two-stage band pass filter (BPS) composed of the two quarter-wavelength tip-short-circuited resonators 411a and 411b, the inter-stage coupling capacitor 412 disposed therebetween, and the input/output coupling capacitors 413a and 413b disposed at the input side and output side thereof.

[0079] Similarly, the receiving filter 408 is a two-stage BPS composed of the two quarter-wavelength tip-short-circuited resonators 414a and 414b, the inter-stage coupling capacitor 415, and the input/output coupling capacitors 416a and 416b. Here, the quarter-wavelength tip-short-circuited resonator 411a, 411b, 414a and 414b constituting the transmitting filter 407 and the receiving filter 408 shown in FIG. 7 are equivalent to the metal foil resonators 107 shown in FIG. 1.

[0080] The inter-stage coupling capacitors 412 and 415 and the input/output coupling capacitors 413a, 413b, 416a and 416b constituting the transmitting filter 407 and the receiving filter 408 are each composed of the multilayered wiring conductor 201 in the substrate 101 and the metal foil resonator 107. Devices which are difficult to form in the substrate 101, such as the diodes 103a to 103e, and SAW filters 102a and 102b, are mounted on the substrate 101, and the strip lines, capacitors and inductors, which can be formed in the substrate 101, are formed in the substrate 101, whereby the complicated RF device can be made compact.

[0081] In addition, since the metal foil resonator 107, which has high conductivity and less irregularity, is used as the resonator, a Quality factor Qc associated with a conductor loss is enhanced. Therefore, a filter or duplexer having a high Quality factor representing the performance of the filter and low loss can be realized. The Quality factor is ex- pressed by the following formula 1 using the Quality factor Qc associated with the conductor loss, a Quality factor Qd associated with a dielectric loss and a Quality factor Qr associated with a radiation loss.

$$1/Q = 1/Q_c + 1/Q_d + 1/Q_r \quad (\text{Formula 1})$$

[0082] Furthermore, according to the embodiment 1, on the upper surface of the metal foil resonator 107, there is provided the substrate 106 made of a high temperature cofired ceramic with high dielectric constant, which has a higher dielectric loss Qd, rather than the substrate 101 made of the low temperature cofired ceramic with low dielectric con-

stant. Thus, the Quality factor of the resonator can be further enhanced. In addition, as the dielectric constant is increased, the length of the resonator can be reduced. Thus, the size of the RF device can be reduced compared to the case where it is formed using only the ceramic with low dielectric constant. Thus, a filter or duplexer having low loss and reduced size can be realized.

[0083] As described above, the duplexer 308 or filters 407, 408 composed of the substrates 101 and 106 with different dielectric constants and areas and the metal foil resonator 107 formed therebetween, the multilayered RF switches composed of the external components, such as the PIN diodes, formed in the substrate 101 made of the low temperature cofired ceramic with low dielectric constant and on the upper surface thereof, and the like are integrated, whereby the compact RF device with low loss capable of supporting the different communication modes, that is, the TDMA and CDMA modes can be realized.

[0084] In the description of this embodiment, the transmitting filter 407 and the receiving filter 408 constituting the duplexer 308 are the two-stage BPFs. However, the filters may be an LPF or band elimination filter (BEF). Furthermore, the number of stages is not limited to two, and may be changed appropriately for a desired characteristic.

[0085] In addition, shielding can be enhanced by providing a ground electrode GND on the whole or part of the surface of the substrate 106 made of the high temperature cofired ceramic with high dielectric constant.

[0086] In the above description, the metal foil resonator 107 is used as an example of the resonator electrode according to this invention. However, instead of the metal foil resonator 107, a printed electrode formed by screen printing or the like can also enhance the dielectric loss Qd due to the substrate 106 made of the high temperature cofired ceramic with high dielectric constant, and thus, a filter or duplexer with low loss can be realized.

[0087] In the above description, the substrate 106 made of the high temperature cofired ceramic with high dielectric constant is provided on the upper surface of the metal foil resonator 107 to enhance the dielectric loss Qd. However, the substrate 106 may be made of the low temperature cofired ceramic with high dielectric constant to enable an electrode to be formed in the substrate 106 by screen printing or the like as in the case of the substrate 101.

[0088] FIG. 14 shows an arrangement example in such a case. The substrate 106 shown in FIG. 14 is composed of stacked substrates 106a, 106b and 106c each made of the low temperature cofired ceramic with high dielectric constant. On a surface of the substrate 106b, there is formed a ground electrode 106g. On a surface of the substrate 106a, there are formed by screen printing input/output coupling capacitors 413a, 413b, 416a and 416b and electrodes 1413a, 1413b, 1416a, 1416b, 1412 and 1415, each of which constitutes a part of the inter-stage coupling capacitors 412 and 415. In this case, the input/output coupling capacitors 413a, 413b, 416a and 416b and the inter-stage coupling capacitors 412 and 415, each of which is an example of a part of the filter according to this invention, are formed on a surface of or in the substrate 106 made of the low temperature cofired ceramic with high dielectric constant. In the RF device thus configured, the low temperature cofired ceramic with high dielectric constant serves as the dielectric of the input/output coupling capacitors 413a, 413b, 416a and 416b and the inter-stage coupling capacitors 412 and 415. Therefore, the size of the capacitors can be reduced, so that the whole size of the RF device can be reduced.

[0089] In addition, in this case, the Quality factors of the inter-stage coupling capacitors 412 and 415 and input/output coupling capacitors 413a, 413b, 416a and 416b can be enhanced, so that the filters 407 and 408 can be reduced in loss.

[0090] In FIG. 14, the substrate 106 is shown to be composed of three layers having the electrodes printed thereon, and the substrate 101 is shown to be composed of four layers having the electrodes printed thereon. However, regardless of the number of the layers having the electrodes printed thereon, the same effect can be attained.

[0091] In addition, the resonator electrodes (that is, the tip-short-circuited resonators 411a, 411b, 414a and 414b) may be formed in the substrate 106 made of a ceramic with high dielectric constant. FIG. 15 shows an arrangement example in such a case. Such an arrangement also can attain the same effect as described above.

[0092] Furthermore, the resonator electrodes may be disposed in the vicinity of the substrate 106, rather than on the surface or in the substrate 106. FIG. 16 shows an arrangement in such an example, in which the tip-short-circuited resonators 411a, 411b, 414a and 414b are disposed in the substrate 101. The substrate 101 shown in FIG. 16 is composed of stacked substrates 101a, 101b, 101c and 101d each made of the low temperature cofired ceramic with low dielectric constant. Also in the case where the tip-short-circuited resonators 411a, 411b, 414a and 414b are disposed in the substrate 101 and are not in contact with the substrate 106 in this way, if the substrate 101a is thin so that the resonators can be affected by the substrate 106, the same effect as described above can be attained even though the resonator electrodes are disposed in the vicinity of the substrate 106.

[0093] In the above description, the tip-short-circuited resonator electrodes 411a, 411b, 414a and 414b serve as the resonator electrodes. Of course, however, a tip-opened half-wavelength resonator may attain the same effect.

[0094] In the above description, the PIN diodes are used in the switch circuit 301 for switching between the transmitting terminal Tx1 and receiving terminal Rx1 for the first frequency band (EGSM) and the switch circuit 302 for switching among the transmitting terminal Tx2, receiving terminal Rx2 for the second frequency band (DCS) and the duplexer 308 for the third frequency band (UMTS). Of course, however, a switching device, such as a GaAs semiconductor, a field effect transistor and a varactor diode, may attain the same effect.

[0095] Furthermore, in this embodiment, the RF device provided for triple bands for three systems, that is, EGSM,

DCS and UMTS systems has been described. However, it is obvious that this invention is not limited thereto and this invention includes any arrangement in which the substrate 101 made of a material with a lower dielectric constant having a first high frequency circuit for a lower frequency band formed therein or on a surface thereof and at least part of a resonator of a second high frequency circuit for a higher frequency band are provided on a surface of the substrate 106, and the first and second high frequency circuits are connected to each other.

[0096] Furthermore, in the description of the embodiment 1, the first high frequency circuit for a lower frequency band is formed in the first substrate and the second high frequency circuit for a higher frequency band is formed in the second substrate. However, as far as no problem of the line impedance arises, the first high frequency circuit for a lower frequency band may be formed in the second substrate (for example, substrate 106) and the second high frequency circuit for a higher frequency band may be formed in the first substrate (for example, substrate 101). In this case, each component of the first high frequency circuit formed in the second substrate can provide a high Quality factor, and thus, if the first high frequency circuit constitutes a filter, the loss thereof can be reduced.

[0097] In addition, the first to third frequency bands should not be limited to those described above. For example, the third frequency band may be a frequency band (800 MHz band) provided for the CDMA-One (R) mode, and the first and second frequency bands may be provided for the PDC mode and the PHS mode, respectively. That is, if the third frequency band is lower than the first or second frequency band, the same effect can be attained. Here, of course, the first to third frequency bands may be provided for modes other than those described above.

(Embodiment 2)

[0098] Now, an RF device according to a second embodiment of this invention will be described with reference to the drawings.

[0099] FIG. 9 is a circuit diagram of the RF device according to the embodiment 2 of this invention. In FIG. 9, reference numerals 501 to 505 denote a metal foil resonator serving as the quarter-wavelength tip-short-circuited resonator, reference numerals 506, 507 denote a series capacitor, reference numerals 508, 509 denote a ground capacitor, reference numerals 510 to 512 denote a coupling inductor, reference numerals 513, 514 denote a coupling capacitor, reference numerals 515, 516 denote a bypass capacitor, reference numeral 517 denotes a capacitor for matching between terminals, reference numeral 518 denotes an inductor for matching between terminals, reference numerals 519 to 523 denotes a switch, reference numerals 524 to 528 denote a switch coupling capacitor, reference numeral 529 denotes an antenna terminal, reference numeral 530 denotes a transmitting terminal, and reference numeral 531 denotes a receiving terminal.

[0100] The series capacitors 506 and 507 are connected to open ends of the resonators 501 and 502, respectively, and the resonators 501 and 502 are connected to each other by the inductor 510, thereby forming a transmitting filter 540. The coupling inductor 510 has the ground capacitors 508 and 509 connected to the ends thereof for suppressing harmonics. On the other hand, the resonators 503, 504 and 505 are coupled with each other by the capacitors 513 and 514. The input/output coupling inductors 511 and 512 are connected to open ends of the resonators 503 and 505, respectively, whereby a receiving band pass filter 541 is formed. In addition, the bypass capacitor 515 bridging the coupling elements 511 and 513 and the bypass capacitor 516 bridging the coupling elements 512 and 514 provide an attenuation pole at a frequency higher than the pass band.

[0101] An output terminal of the transmitting filter 540 and an input terminal of the receiving band pass filter 541 are connected to the antenna terminal 529 via the series inductor 518 and the parallel capacitor 517 both for matching between terminals. The switches 519, 520, 521, 522 and 523 are connected to open ends of the resonators 501, 502, 503, 504 and 505 via the switch coupling capacitors 524, 525, 526, 527 and 528, respectively. The other ends of the switches are all grounded. In this way, the transmitting filter 540, the receiving band pass filter 541, the transmitting terminal 530, the receiving terminal 531 and the antenna terminal 529 constitute the RF device.

[0102] FIG. 10 shows a specific circuit arrangement of the switches 519 to 523 including a PIN diode. Reference numeral 601 denotes a PIN diode. The PIN diode 601 is serially connected to a coupling capacitor 602 for blocking a direct current (equivalent to the capacitors 524 to 528 in FIG. 9) to form a frequency shift circuit. A control terminal 606 is connected to the connection between the PIN diode 601 and the coupling capacitor 602 via a resistor 605, a bypass capacitor 604 and a choke coil 603. A shift voltage is applied to the control terminal 606 to control the switching among bands.

[0103] That is, the shift voltage applied to the control terminal 606 is intended to turn on or off the PIN diode 601. If a certain positive voltage (shift voltage) higher than a bias voltage applied to a cathode of the PIN diode 601 is applied to the control terminal 606, a resistance of the PIN diode 601 in the forward direction becomes quite low, so that a current flows in the forward direction, and thus, the PIN diode 601 is turned on. The resistor 605 is to control the current value of the PIN diode 601 when it is in the on state. To the contrary, if a voltage of 0 volts or a reverse bias voltage is applied to the control terminal 606, the resistance of the PIN diode 601 in the forward direction becomes quite high, so that no current flows in the forward direction, and thus, the PIN diode 601 is turned off.

[0104] FIG. 11 is a partial perspective view of the RF device according to the embodiment 2 of this invention, in which the same parts as in FIG. 10 are as signed the same reference numerals. Reference numeral 701 denotes a metal foil resonator, reference numeral 702 denotes a substrate made of a ceramic with low dielectric constant, which is an example of the first substrate according to this invention, reference numeral 703 denotes a substrate made of a ceramic with high dielectric constant, which is an example of the second substrate according to this invention, and reference numeral 704 denotes a thermosetting resin.

[0105] A plurality of metal foil resonators 701 are equivalent to the resonators 501 to 505, and the metal foil resonators 701 are interposed between a lower substrate 702 and an upper substrate 703. Spaces between the metal foil resonators 701 are filled with the thermosetting resin 704, which interconnects and integrates the substrates 702 and 703. The components constituting the RF device according to the second embodiment of this invention except for the resonators 501 to 505, such as capacitors, inductors and switches, are mounted on the substrate 702 made of the ceramic with low dielectric constant.

[0106] That is, the high frequency circuit is formed in or on a surface of the substrate 702 except for a part of the filter (that is, the metal foil resonators), and the metal foil resonators 701, each of which is an example of at least part of the filter according to this invention, are formed on a surface of the substrate 703.

[0107] FIG. 12 shows a transfer characteristic of the RF device according to the embodiment 2 of this invention. FIG. 12 (a) shows a transfer characteristic of the transmitting filter 540 composed of the transmission line from the transmitting terminal 530 to the antenna terminal 529, the resonators 501 and 502 connected to the transmission line via the series capacitors 506 and 507, respectively, and the inter-stage coupling inductor 510. The coupling inductor 510, the series inductor 518 connected to the output terminal of the transmitting filter 540, and the ground capacitors 508, 509 and 517 provide a low pass characteristic to suppress harmonics in a transmitting band.

[0108] The inductor 518 and capacitor 517 serve also to adjust the impedances of the transmitting filter 540 and receiving band pass filter 541 to prevent the filters from affecting each other in their respective frequency bands at the antenna terminal 529. Since the impedances of the transmitting filter 540 and the receiving band pass filter 541 are adjusted in this way, the transmitting filter 540 exhibits a low insertion loss for the sent signal in the transmitting frequency band, which is the pass band, and therefore, can transmit the sent signal from the transmitting terminal 530 to the antenna terminal 529 with little attenuation of the sent signal.

[0109] On the other hand, the transmitting filter 540 exhibits a high insertion loss for the received signal in the receiving frequency band, and therefore, reflects most of the input signal in the receiving frequency band. Thus, the received signal inputted through the antenna terminal 529 is directed toward the receiving band pass filter 541.

[0110] FIG. 12(b) shows a transfer characteristic of the receiving band pass filter 541 composed of the transmission line from the antenna terminal 529 to the receiving terminal 531, the grounded resonators 503, 504 and 505, the inter-stage coupling capacitors 513 and 514, and the input/output coupling inductors 511 and 512. The impedance characteristic of the receiving band pass filter 541 and the impedances of the capacitors 515 and 516 used in the bypass circuit provide an attenuation pole as shown in FIG. 12(b).

[0111] In the circuit arrangement shown in FIG. 9, since the inductors are used for coupling of the input and the output, the impedance of the bypass circuit is equivalently inductive, and the attenuation pole appears in a region in the vicinity of a frequency where the impedance of the receiving band pass filter 541 becomes capacitive, that is, a transmitting frequency higher than a center frequency of the receiving band pass filter 541.

[0112] The receiving band pass filter 541 exhibits a low insertion loss for the received signal in the receiving frequency band and can transmit the received signal from the antenna terminal 529 to the receiving terminal 531 with little attenuation of the received signal. On the other hand, the receiving band pass filter 541 exhibits a high insertion loss for the sent signal in the transmitting frequency band and therefore, reflects most of the input signal in the transmitting frequency band. Thus, the sent signal from the transmitting filter 540 is directed toward the antenna terminal 529.

[0113] In addition, to the open ends of the resonators 501, 502, 503, 504 and 505, there are connected frequency shift circuits composed of series connections of the switch coupling capacitors 524, 525, 526, 527 and 528 for blocking a direct current and the switches 519, 520, 521, 522 and 523 each having one end grounded, respectively.

[0114] That is, a resonance frequency of the resonators 501 to 505 is determined by a capacitance component and inductance component of the respective resonators and a capacitance of their respective frequency shift circuits at the time when their respective switches 519 to 523 are in the on state or off state. If any of the switches 519 to 523 is turned on, the capacitance component of the frequency shift circuit is increased, and accordingly, the resonance frequency of the resonator is reduced. As a result, the blocking band of the transmitting filter 540 and the center frequency and pass band of the receiving band pass filter 541 are shifted to a lower frequency. On the other hand, if any of the switches 519 to 523 is turned off, the capacitance component of the frequency shift circuit is reduced, and accordingly, the resonance frequency of the resonator is increased. As a result, the blocking band of the transmitting filter 540 and the pass band of the receiving band pass filter 541 are shifted to a higher frequency. In other words, the blocking band of the transmitting filter 540 and the pass band of the receiving band pass filter 541 can be shifted synchronously by operating the switches 519 to 523 in this way.

[0115] FIG. 12 shows relationships between the transfer characteristics of the transmitting filter 540 and receiving band pass filter 541 configured as described above and the on or off state of the switches 519 to 523 in a frequency region from 800 to 1000 MHz. Reference numeral 801 in FIG. 12(a) and reference numeral 803 in FIG. 12(b) designate the transfer characteristic in the case where all of the switches 519 to 523 are turned on, and reference numeral 802 in FIG. 12(a) and reference numeral 804 in FIG. 12(b) designate the transfer characteristic in the case where all of the switches 519 to 523 are turned off. In this way, by switching of the switches 519 to 523, the send-side blocking frequency band and the receive-side frequency pass band of the RF device are changed synchronously.

[0116] Besides the PIN diode described above, a transistor may serve as the switches 519 to 523. For example, FIG. 13 shows a case where a field effect transistor (FET) 901 serves as the switches 519 to 523. A gate electrode of the FET 901 is connected to a control terminal 903 via a bypass capacitor 902. Since the FET 901 is a voltage control device, no current is consumed when the device is turned on, unlike the case of the PIN diode. Thus, using such a FET 901 can reduce current consumption. Besides, if a varactor diode serves as the switches 519 to 523, the send-side blocking band and the receive-side pass band can be change continuously.

[0117] As described above, according to this embodiment, the blocking band of the transmitting filter 540 and the pass band of the receiving band pass filter 541 of the RF device can be controlled synchronously by the current or voltage applied thereto externally. Therefore, even if a certain wide band is required, an attenuation can be provided without increasing the number of the stages of each filter. In addition, since the number of the stages is small, the loss is reduced. As a result, the RF device itself can be downsized.

[0118] In addition, since the metal foil resonator is used as the resonator, the Quality factor of the resonator is enhanced. And, since the substrate made of the high temperature cofired ceramic with high dielectric constant having a good high frequency characteristic is overlaid on the upper surface of the metal foil resonator, the Quality factor of the resonator is further enhanced. As a result, each of the filters can be reduced in loss.

[0119] In the above description, the transmitting filter 540 is arranged on the transmitting side and the receiving band pass filter 541 is arranged on the receiving side. However, such an arrangement of the transmitting filter and receiving filter is obviously susceptible to various modifications, such as using a low pass filter, and of course, the modifications are included in this invention.

[0120] Besides, while the resonator devices 501, 502 and the impedance varying devices 519, 520, which are connected to each other in parallel by the capacitors, may be connected to each other by inductors.

[0121] This invention is the most effective if it is applied to a communication apparatus for a system with wide transmitting pass band and receiving pass band and a narrow interval between the transmitting pass band and the receiving pass band, such as PCS, EGSM, and CDMA in Japan. However, a system other than those described above may be contemplated.

[0122] For example, in another system, the transmitting pass band and the receiving pass band are each divided, with bandwidths thereof corresponding to each other, into two bands, that is, a transmitting Low band and a transmitting High band, and a receiving Low band and a receiving High band, respectively. For the respective two divisional bands, a control signal is used to switch between the transmitting band and the receiving band synchronously, with the transmitting Low band being associated with the receiving Low band and the transmitting High band being associated with the receiving High band. This is equivalent to widening the interval between the transmitting frequency and the receiving frequency during operation of the system, and thus, an attenuation can be ensured without increasing the number of the stages of each filter. Here, in this system, by selecting the band including the channel to be used by the control signal, whole of the transmitting pass band and receiving pass band can be covered. In addition, of course, the arrangement according to this invention can be applied to other systems including TDMA and CDMA.

[0123] In addition, since some or all of the capacitors and inductors except for the resonators 501 to 505 are composed of electrodes in the substrate 702 made of the ceramic with low dielectric constant, downsizing can be realized.

[0124] The configuration of each substrate in the RF device according to this embodiment may be the same as that according to the embodiment 1 (shown in FIGS. 13 to 16). That is, the substrate 702 may be equivalent to the substrate 101 and the substrate 703 may be equivalent to the substrate 106.

[0125] The RF device according to this embodiment has been described so far to operate while supporting only one system in the description. However, it may operate while supporting a plurality of systems.

[0126] The configuration of the RF device described so far, in which one substrate made of a ceramic with high dielectric constant is overlaid on another substrate made of a ceramic with low dielectric constant, is not limited to those shown in FIGS. 1 and 11, and may be those shown in FIGS. 2, 3 and 4.

[0127] In the case where the two substrates 106 are disposed on the substrate 101 with spaced apart from each other as shown in FIG. 2, if the transmitting filter 407 is constituted by one of the substrates 106 and the substrate 101 and the receiving filter 408 is constituted by the other of the substrates 106 and the substrate 101, the transmitting filter 407 and the receiving filter 408 can be prevented from interfering with each other, and therefore, a high performance RF device can be provided.

[0128] In the above description, the RF device according to this invention has been described to be composed of

the substrate 101 or 702 made of a ceramic with low dielectric constant and the substrate 106 or 703 made of a ceramic with high dielectric constant overlaid thereon. However, the substrate 101 or 702 and the substrate 106 or 703 may be arranged side by side.

[0129] FIG. 17 shows an arrangement in which the substrates 101 and 106 are arranged side by side and a high frequency circuit formed on or in the substrate 101 and a high frequency circuit formed in the substrate 106 are connected to each other through the wiring pattern 201. In such a case, the same effect as described above can be attained.

[0130] As described above, according to this invention, the metal foil is used for the resonator constituting the duplexer and a ceramic with high dielectric constant having a good material characteristic is provided on the upper surface of the resonator, whereby the resonator with low loss can be provided. Furthermore, external components arranged in or on the upper surface of the low temperature cofired ceramic with low dielectric constant constitute multilayered switches for a plurality of systems, and the duplexer is formed on the upper surface thereof, whereby a compact RF device with low loss provided also for the TDMA and CDMA can be provided.

[0131] According to this invention, an RF device having a low filter loss and not suffering from a problem about a line impedance, or a compact RF device not suffering from a problem about a line impedance can be provided.

Claims

1. An RF device, comprising:

a first substrate made of a material with a lower relative dielectric constant and having a high frequency circuit formed therein or on a surface thereof; and
a second substrate made of a material with a higher relative dielectric constant,

wherein at least a part of a filter is provided in, on a surface of or in the vicinity of said second substrate and connected to said high frequency circuit, and
said high frequency circuit is composed of an element other than said part of the filter.

2. The RF device according to claim 1, wherein said at least a part of the filter forms a high frequency circuit for a CDMA mode.

3. The RF device according to claim 1, wherein said second substrate is partially overlaid on said first substrate, a semiconductor device or passive device is provided on a region in the surface of said first substrate on which said second substrate is not overlaid, and a multilayered wiring pattern made of copper or silver is formed in said first substrate, whereby said high frequency circuit is formed.

4. The RF device according to claim 3, wherein said semiconductor device includes any one of a PIN diode device, a GaAs semiconductor device, a field effect transistor (FET) device and a varactor diode device, and switching among a plurality of frequency bands is realized by an operation of any one of said devices.

5. An RF device, comprising:

a first substrate made of a material with a lower relative dielectric constant and having a first high frequency circuit for a lower frequency band formed therein or on a surface thereof; and
a second substrate made of a material with a higher relative dielectric constant,

wherein at least a part of a filter of a second high frequency circuit for a higher frequency band is provided in, on a surface of or in the vicinity of said second substrate, and said first high frequency circuit and said second high frequency circuit are connected to each other.

6. The RF device according to claim 5, wherein said second substrate is overlaid on said first substrate, and said part of the filter is sandwiched between said first substrate and said second substrate.

7. The RF device according to claim 6, wherein said second substrate is partially overlaid on said first substrate, a semiconductor device or passive device is provided on a region in the surface of said first substrate on which said second substrate is not overlaid, and a multilayered wiring pattern made of copper or silver is formed in said first substrate, whereby said first high frequency circuit is formed.

8. The RF device according to claim 7, wherein said second substrate comprises a plurality of substrates disposed on said first substrate with spaced apart from each other, one of said plurality of substrates constitutes a transmitting filter, and another of said plurality of substrates constitutes a receiving filter.
- 5 9. The RF device according to claim 5, wherein said lower frequency band is a frequency band for a TDMA mode, and said higher frequency band is a frequency band for a CDMA mode.
- 10 10. The RF device according to claim 5, wherein each of said first and second substrates is composed of a multilayered and integrally molded ceramic.
- 10 11. The RF device according to claim 5, wherein said first substrate is made of a low temperature cofired ceramic and said second substrate is made of a high temperature cofired ceramic.
- 15 12. The RF device according to claim 6, wherein a part of said filter is a resonator electrode, and said resonator electrode is constituted by a metal foil.
13. The RF device according to claim 12, wherein the RF device is integrated by filling a space defined by said first substrate, said second substrate and said resonator electrode with a thermosetting resin.
- 20 14. The RF device according to claim 7, wherein said semiconductor device includes any one of a PIN diode device, a GaAs semiconductor device, a field effect transistor (FET) device and a varactor diode device, and switching between said first high frequency circuit and said second high frequency circuit is realized by an operation of any one of said devices.
- 25 15. The RF device according to claim 5, wherein whole or a part of said second substrate is covered with a shielding electrode.
16. The RF device according to claim 7, wherein said passive device includes a SAW filter with an electrode hermetically sealed.
- 30 17. A communication apparatus, comprising the RF device according to any one of claims 1 to 16, a transmitting circuit, a receiving circuit and an antenna which are connected to said RF device.

Fig. 1

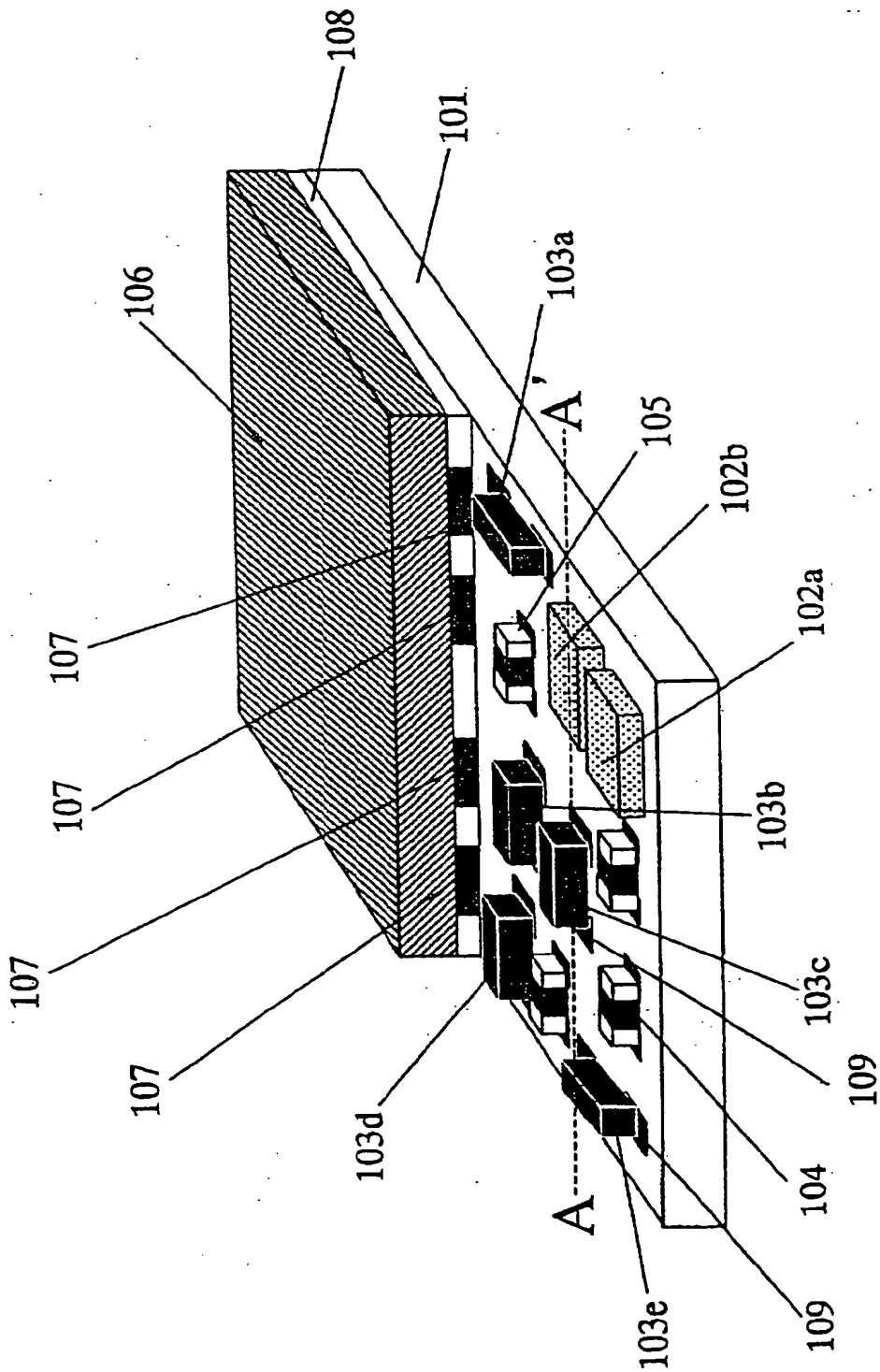


Fig. 2

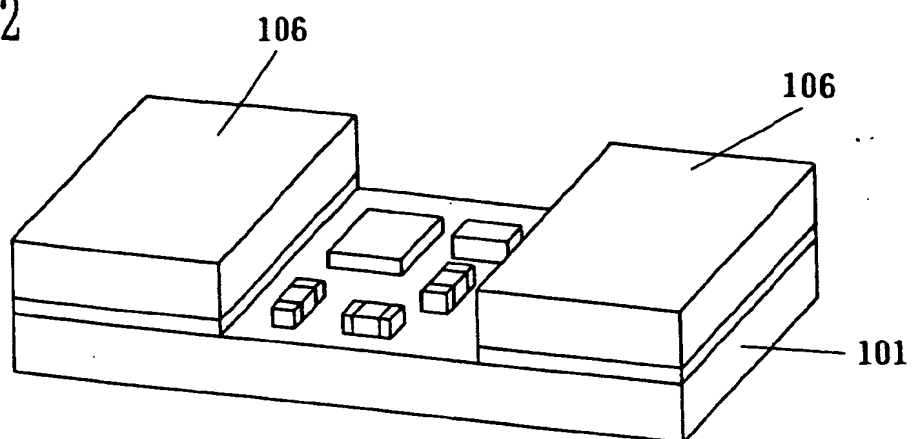


Fig. 3

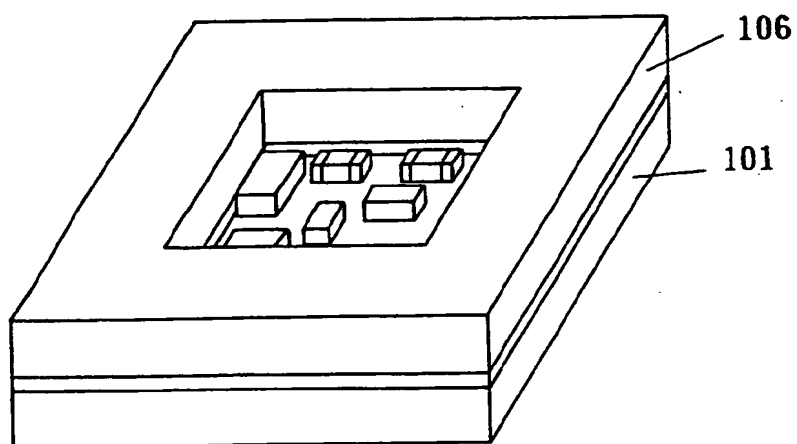


Fig. 4

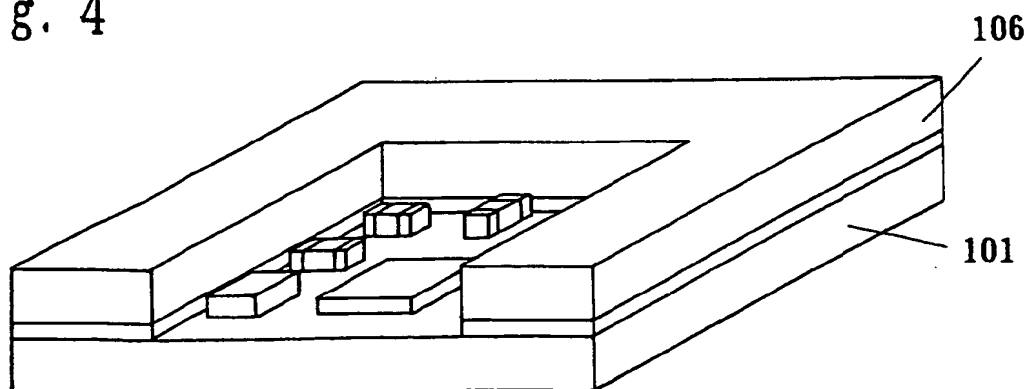


Fig. 5

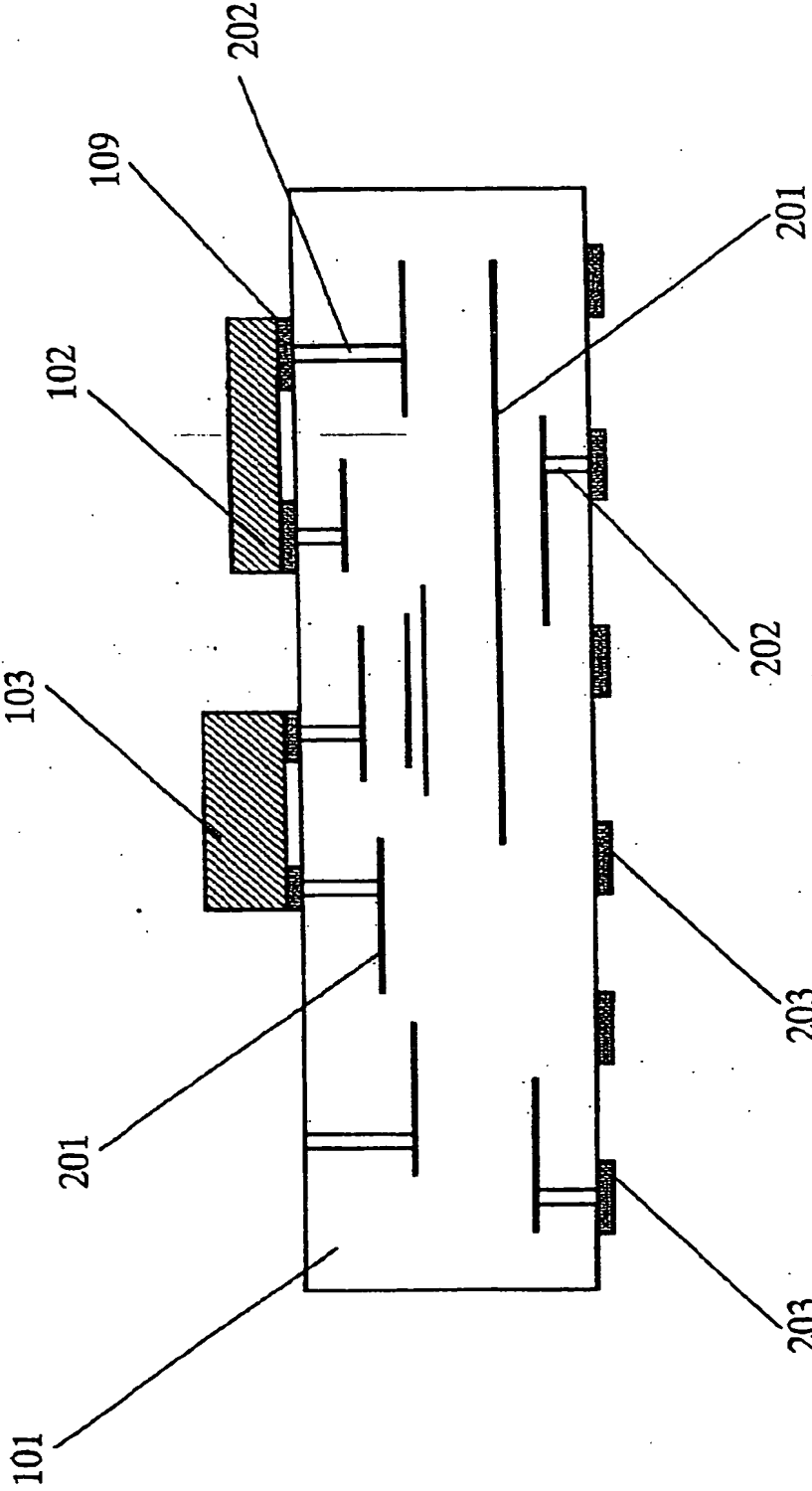


Fig. 6

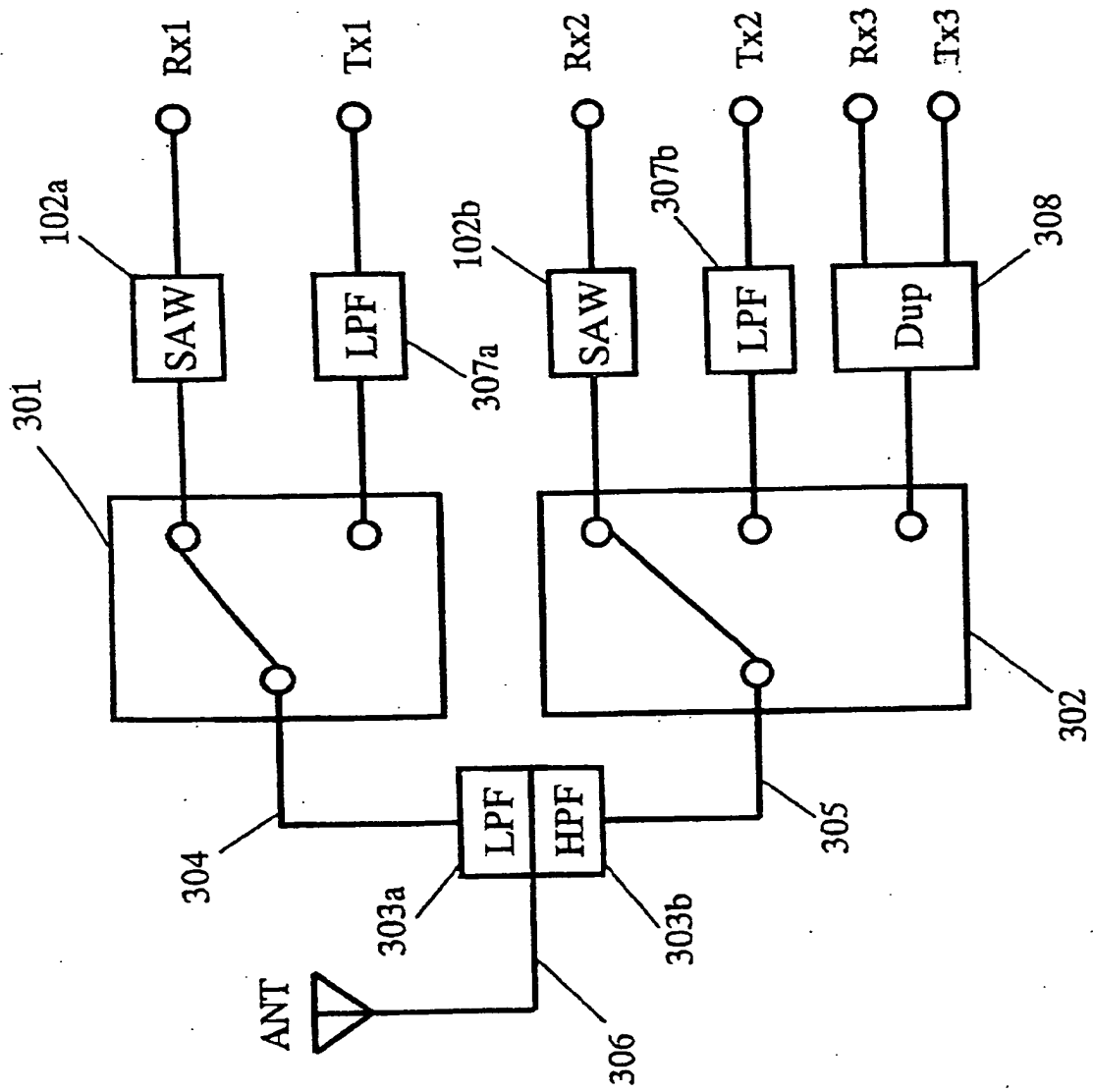


Fig. 7

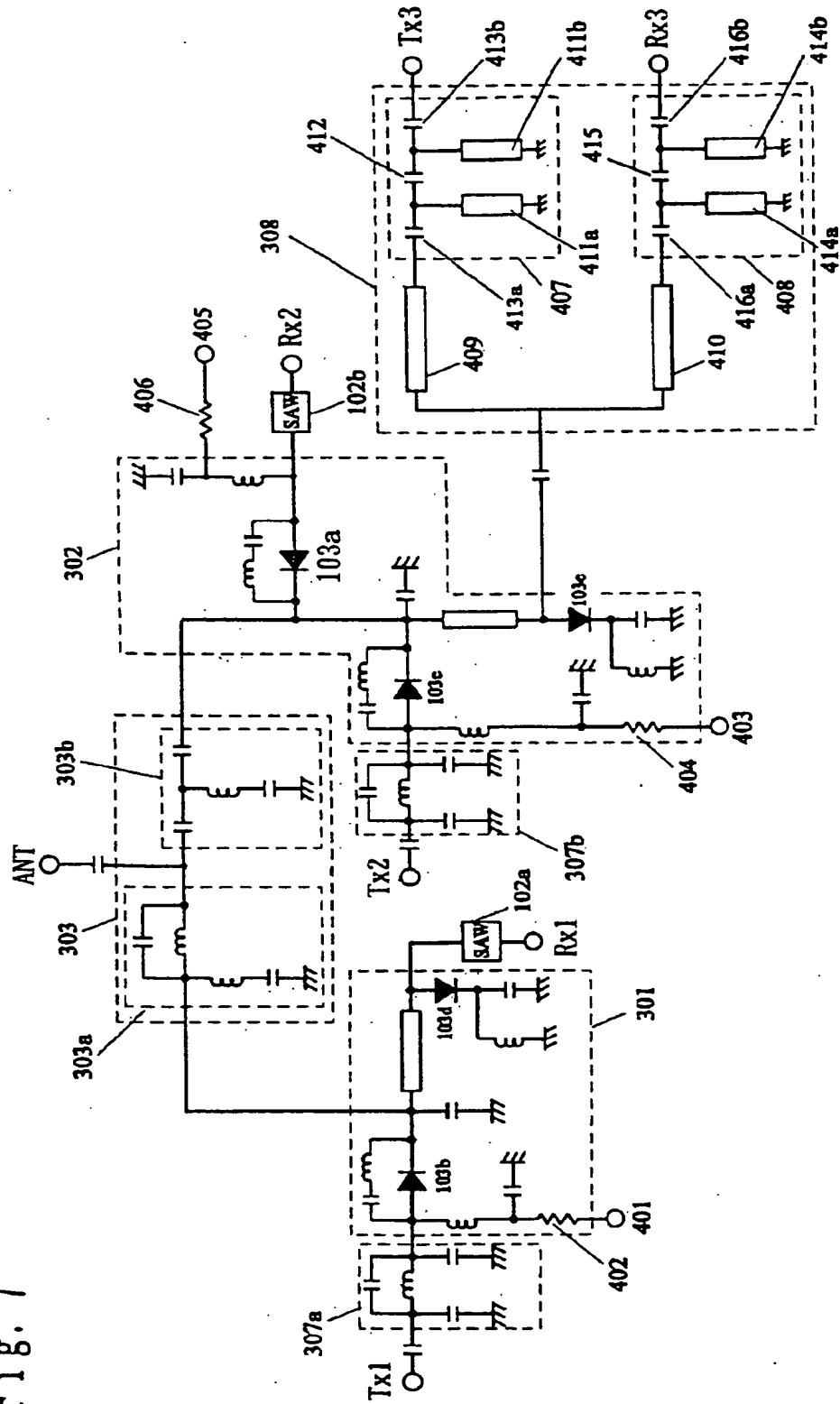


Fig. 8

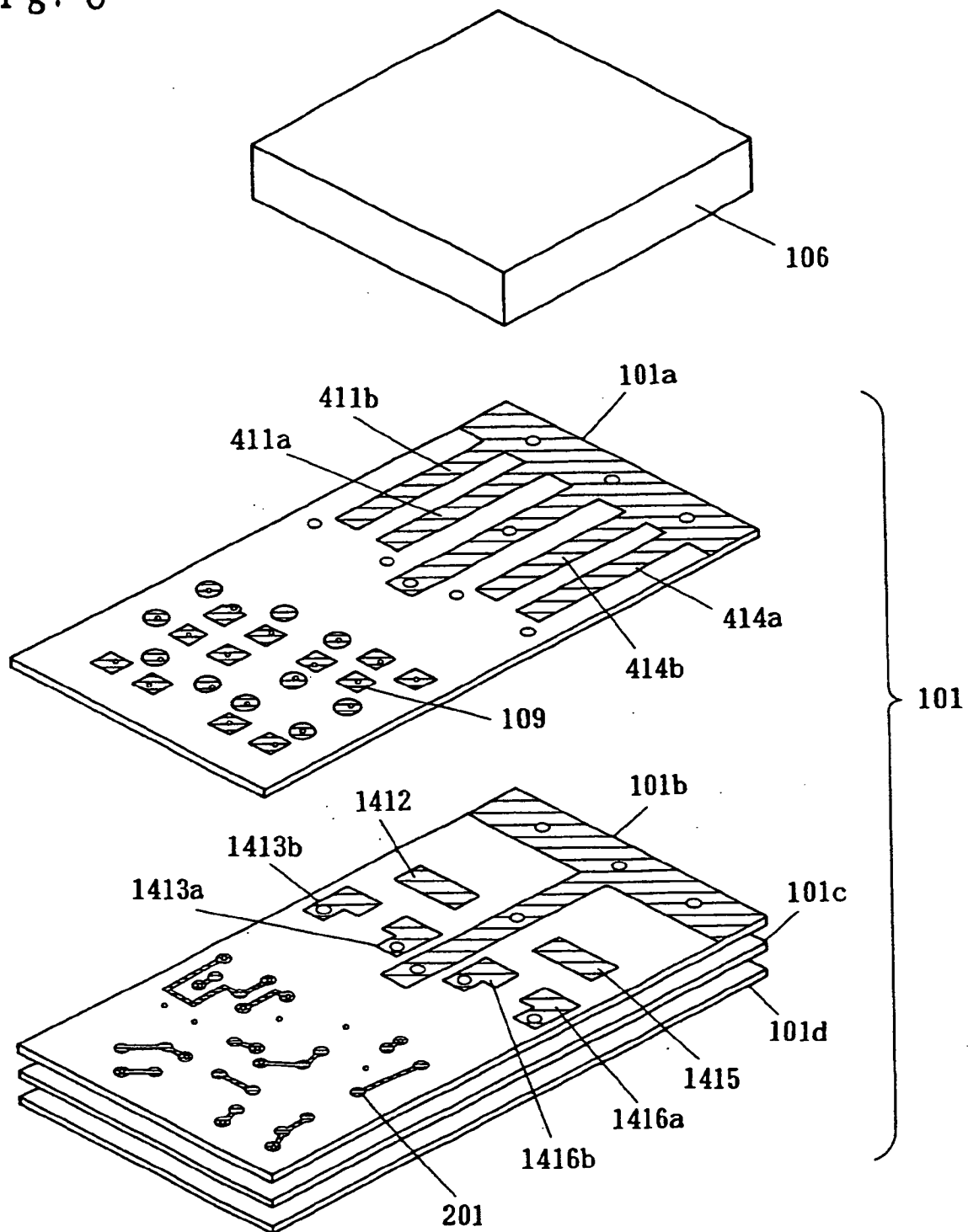


Fig. 9

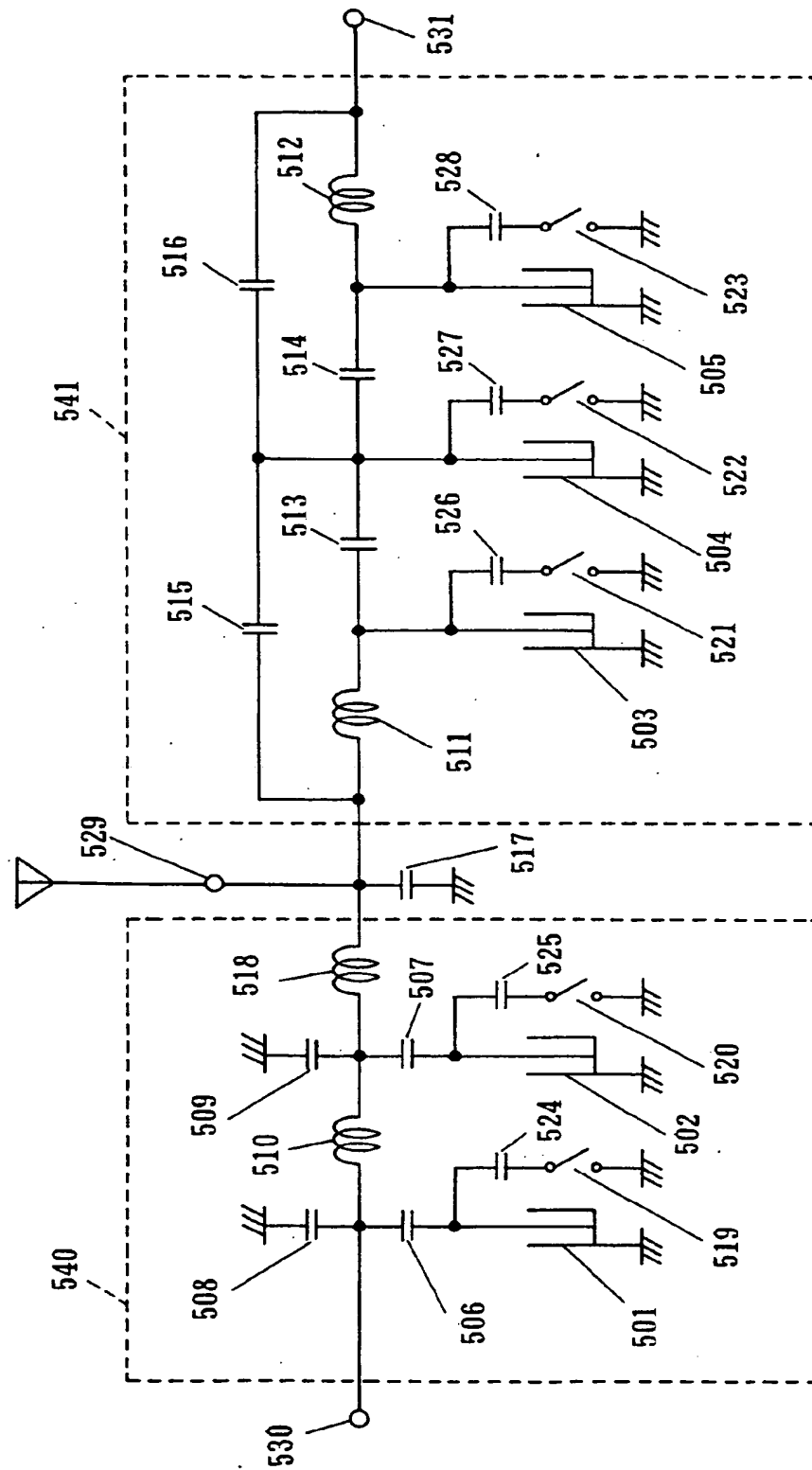


Fig. 10

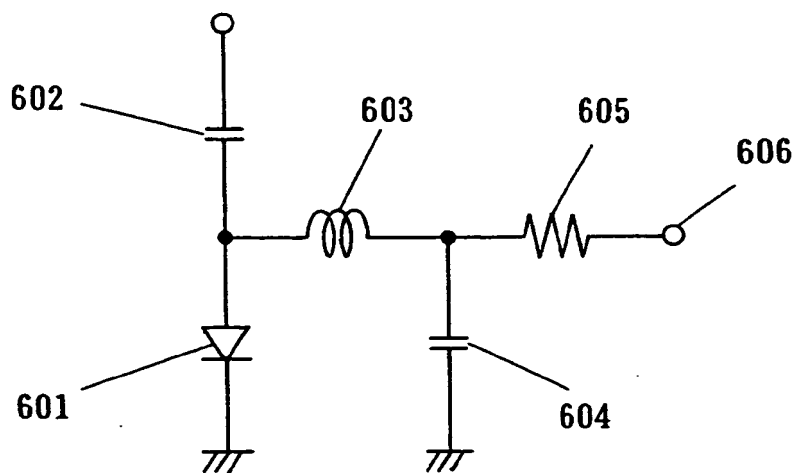


Fig. 11

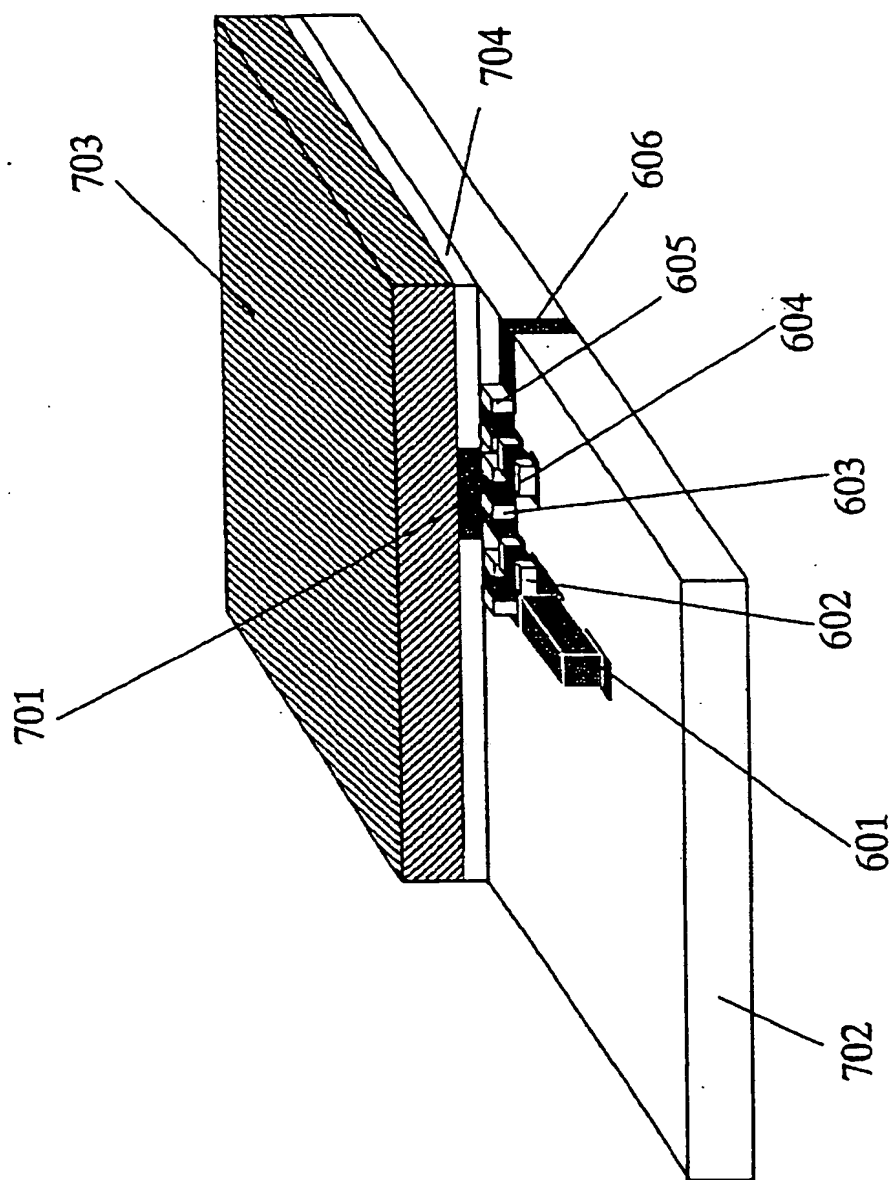


Fig. 12 (a)

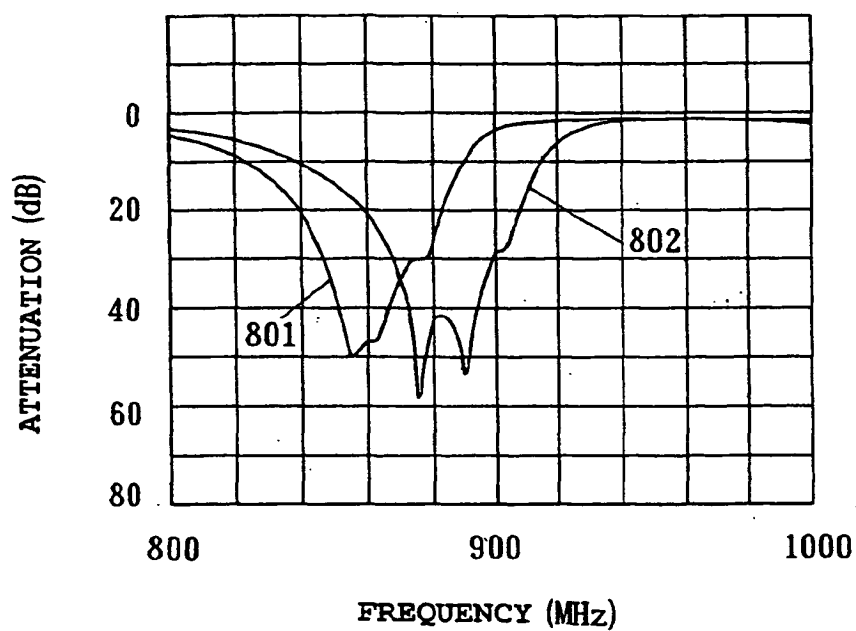


Fig. 12 (b)

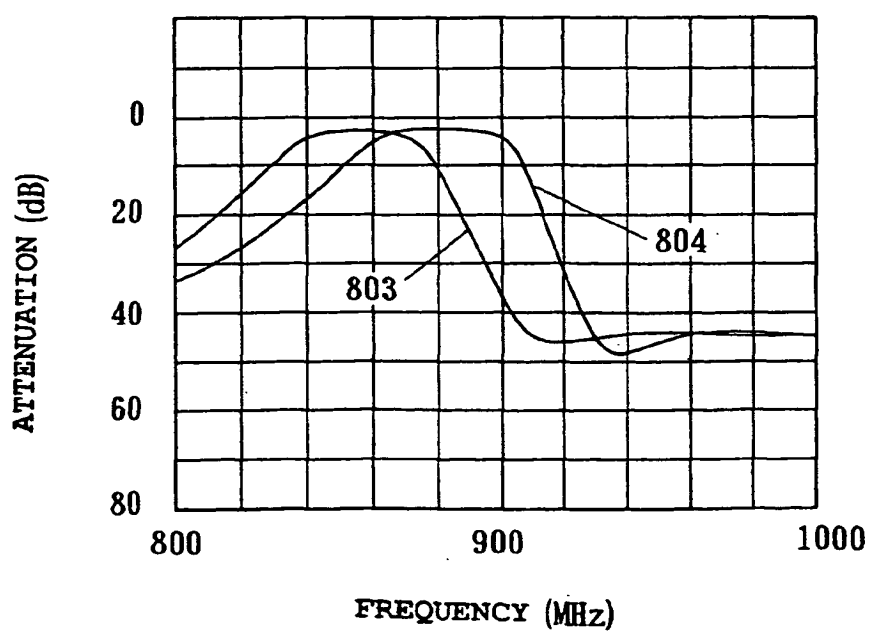


Fig. 13

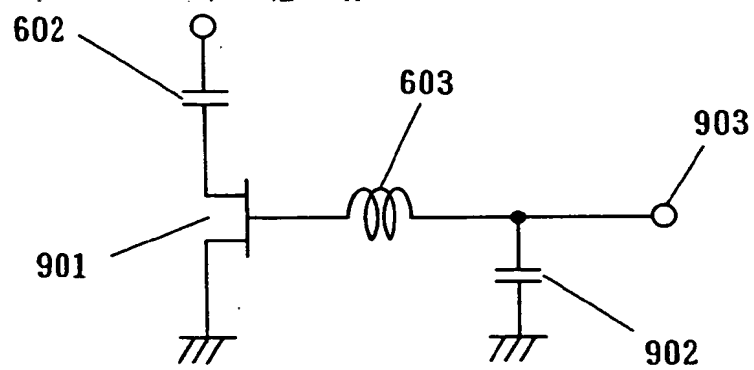


Fig. 14

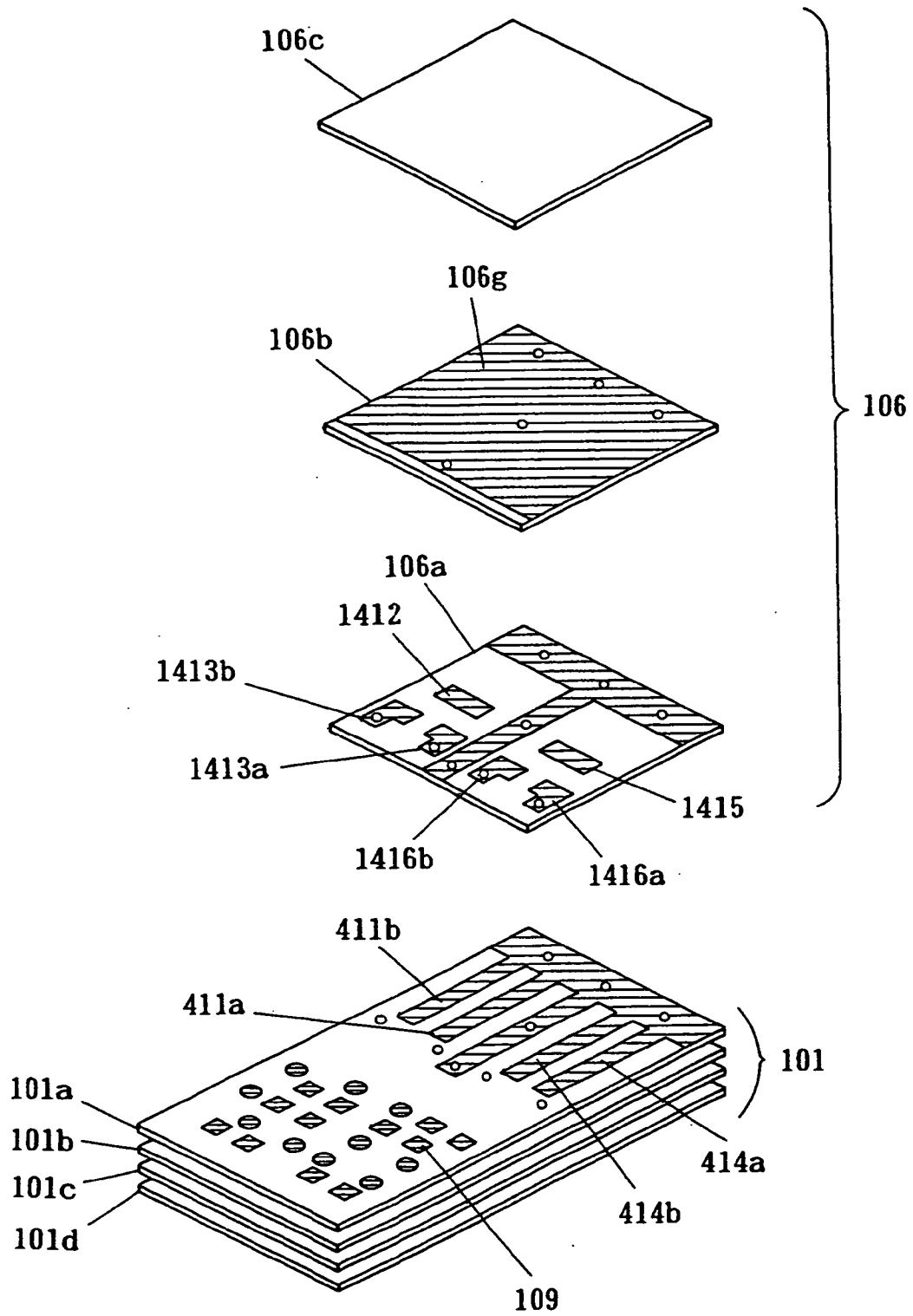


Fig. 15

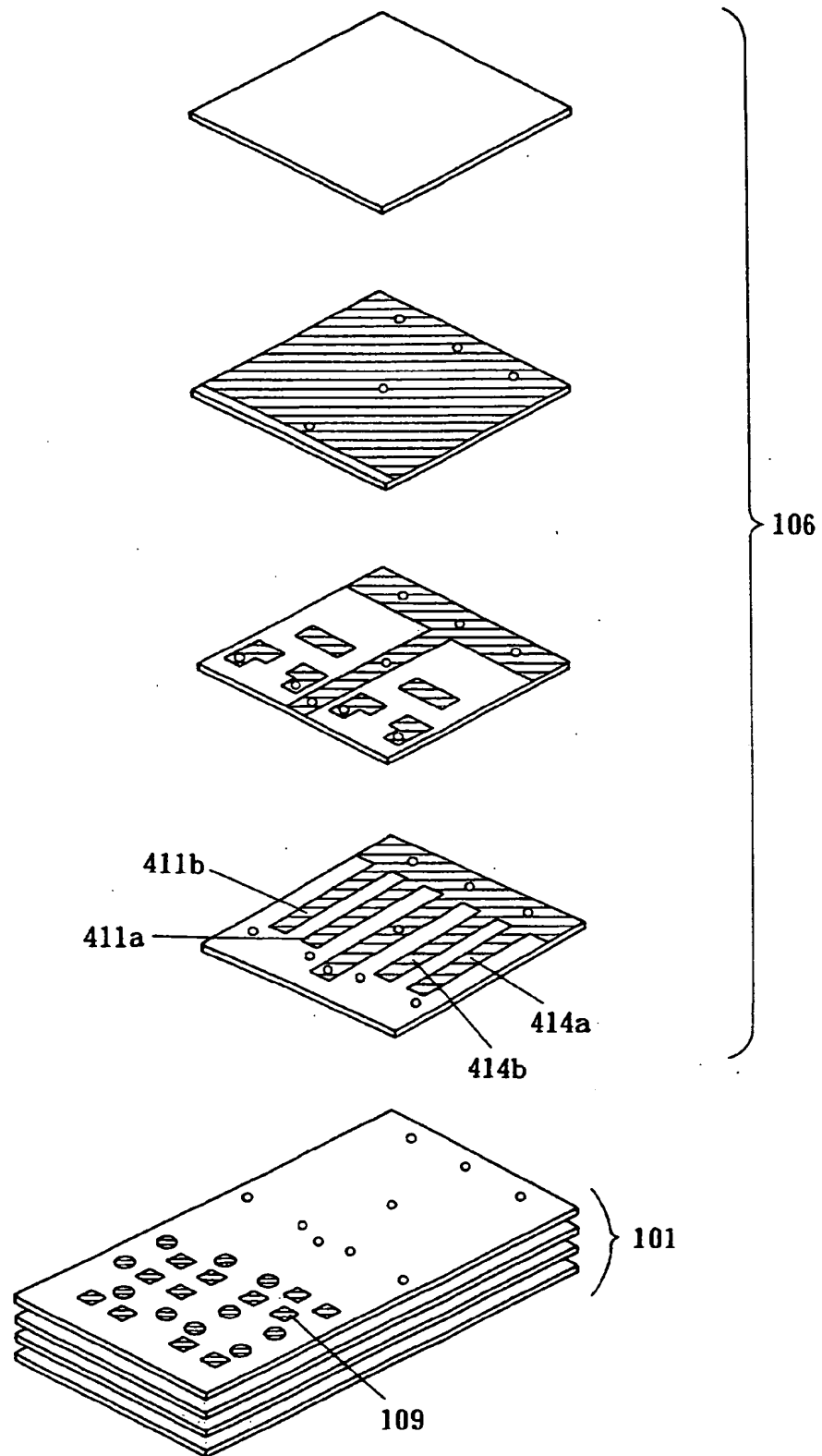


Fig. 16

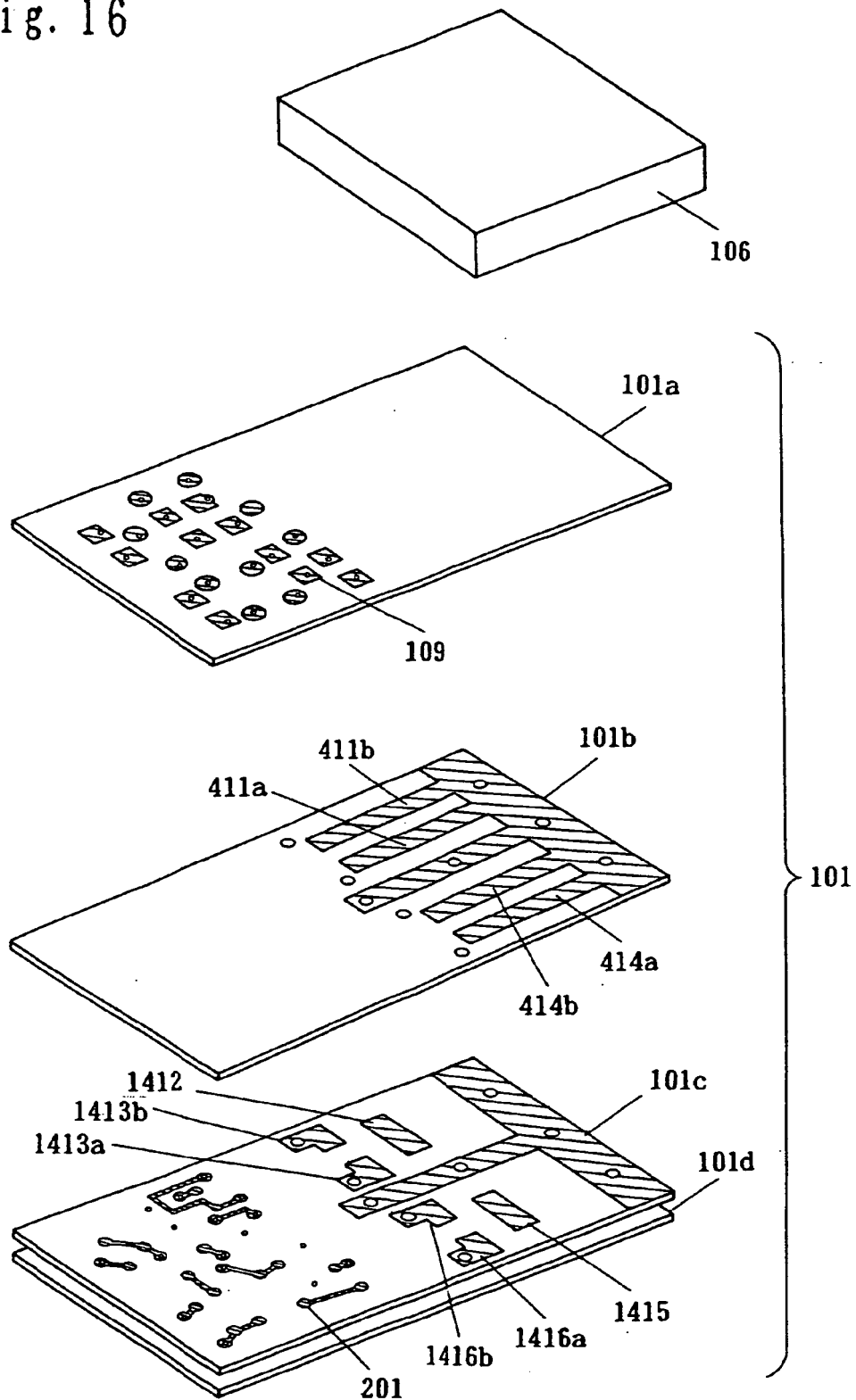


Fig. 17

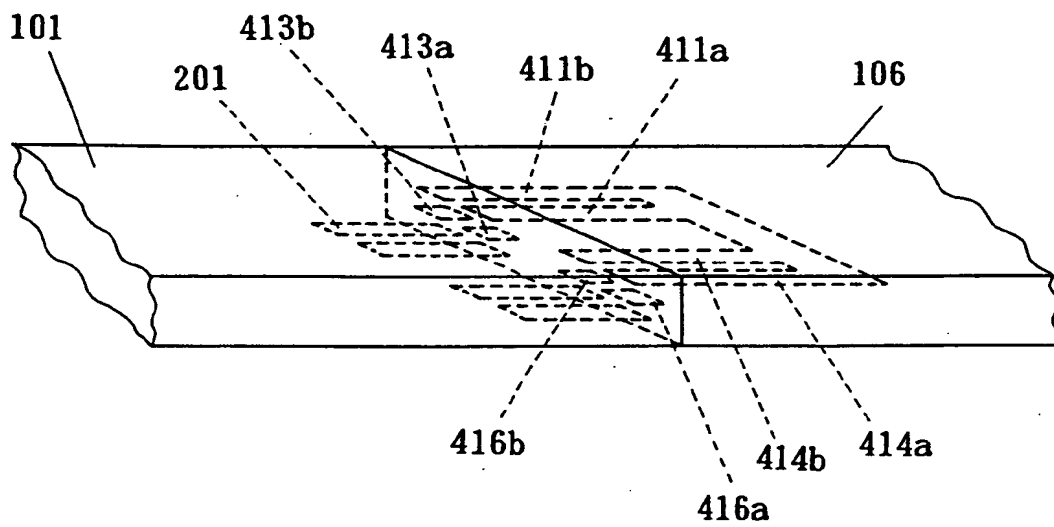


Fig. 18 PRIOR ART

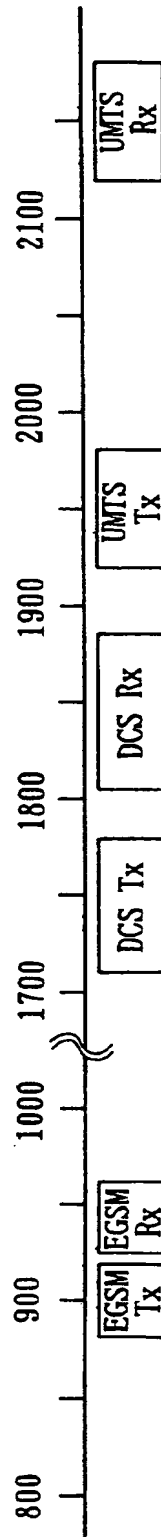


Fig. 19 PRIOR ART

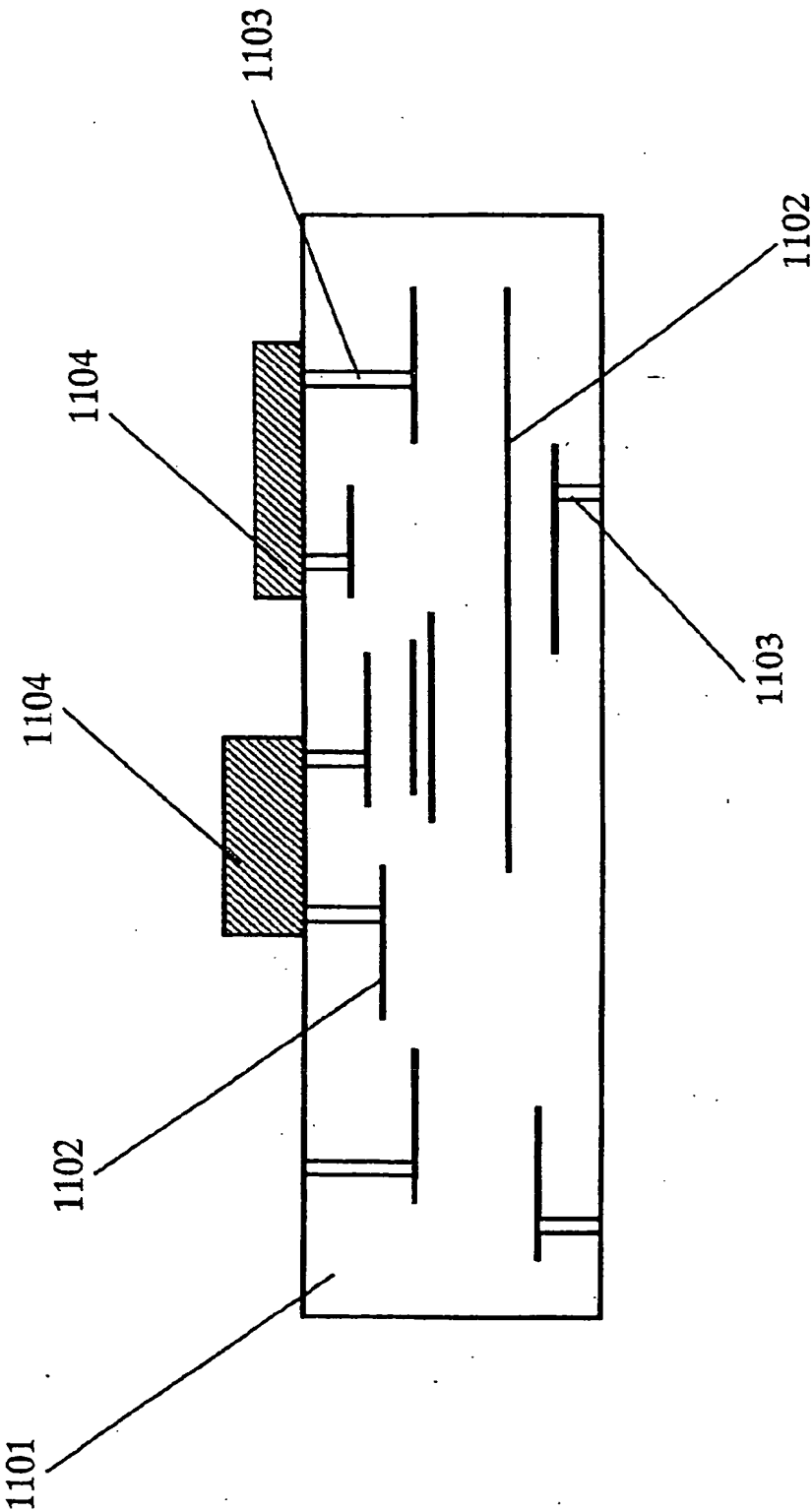


Fig. 20 PRIOR ART

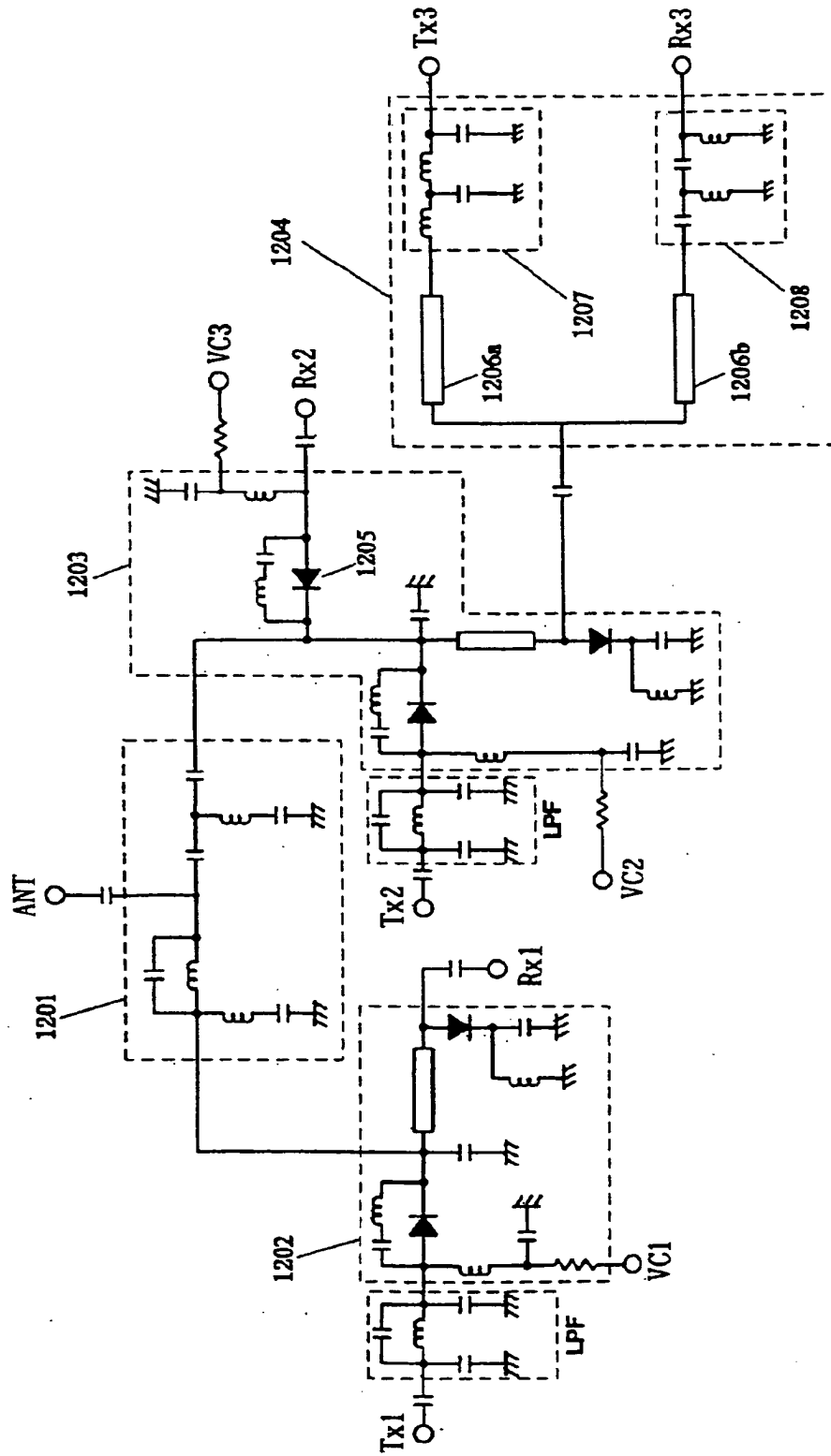


Fig. 21 PRIOR ART

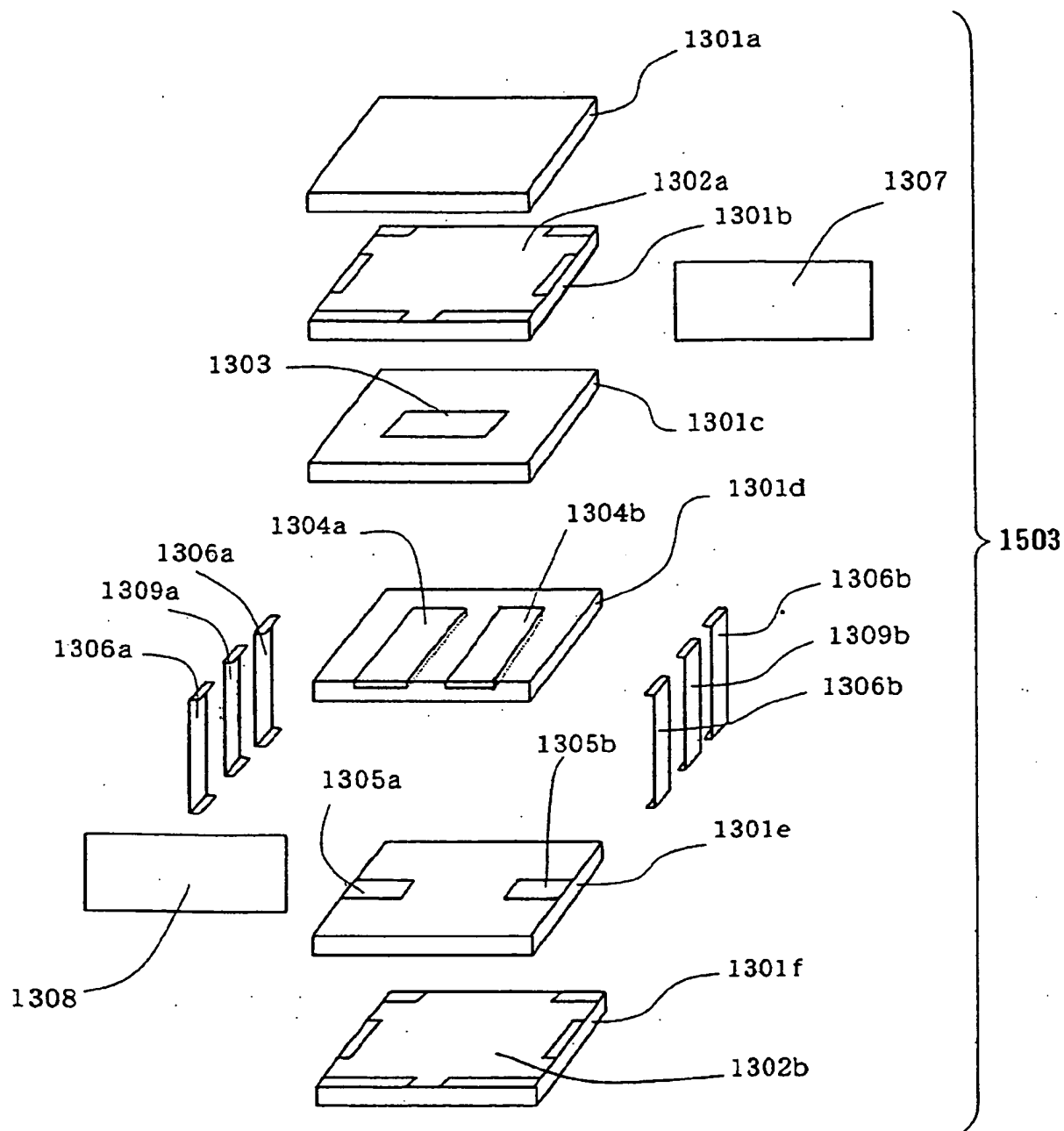


Fig. 22 PRIOR ART

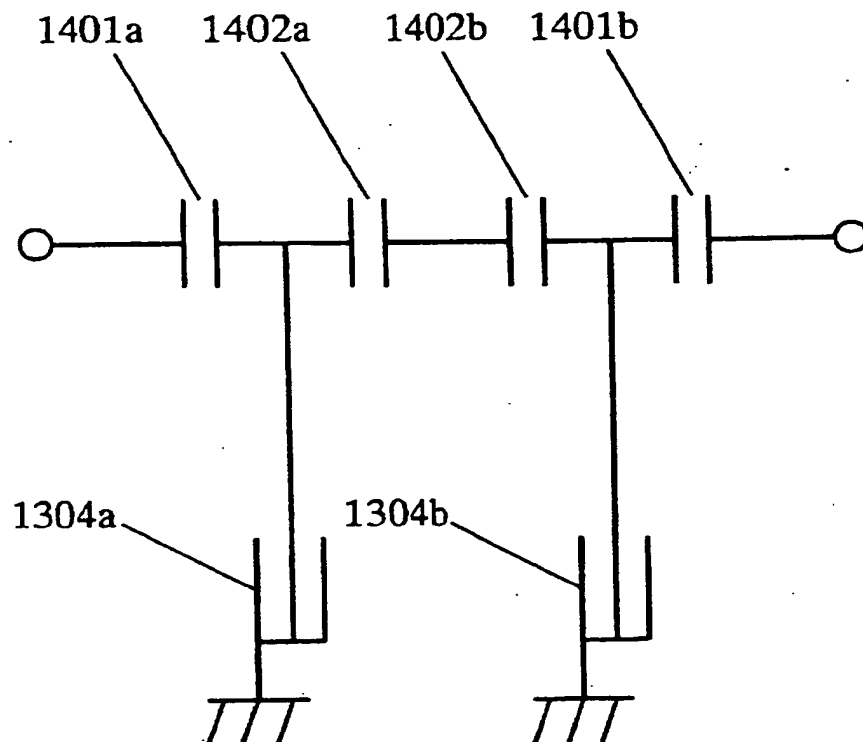
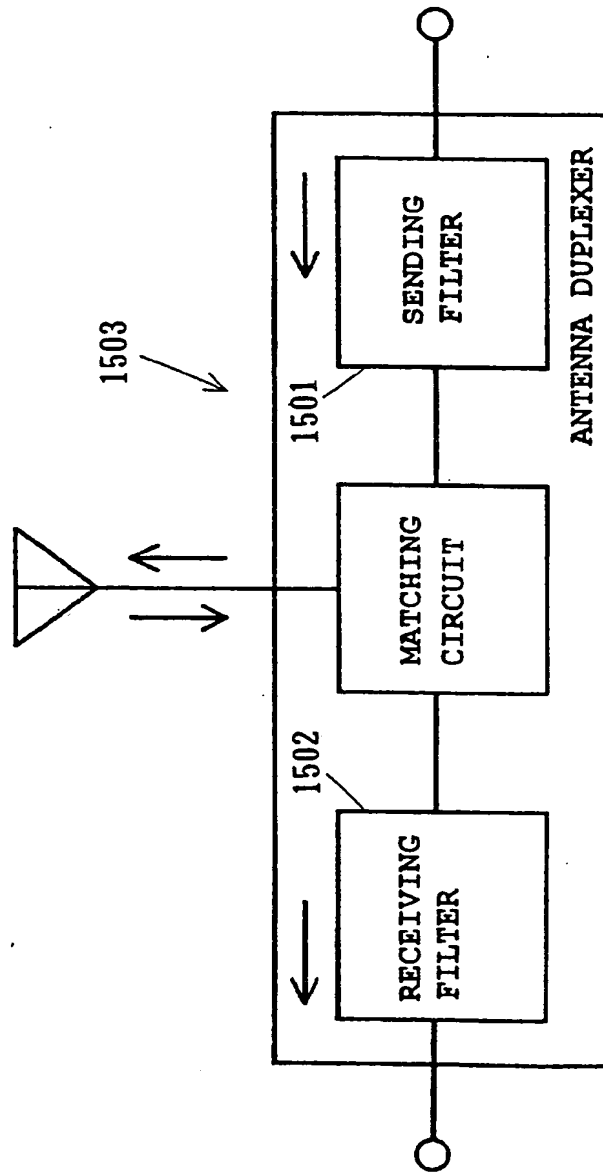
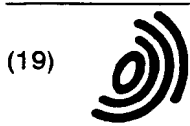


Fig. 23 PRIOR ART



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(11) EP 1 291 954 A3

(12) EUROPEAN PATENT APPLICATION

(88) Date of publication A3:
19.11.2003 Bulletin 2003/47

(51) Int Cl.7: H01P 1/15, H01P 1/203,
H01P 1/213

(43) Date of publication A2:
12.03.2003 Bulletin 2003/11

(21) Application number: 02019050.0

(22) Date of filing: 27.08.2002

(84) Designated Contracting States:
AT BE BG CH CY CZ DE DK EE ES FI FR GB GR
IE IT LI LU MC NL PT SE SK TR
Designated Extension States:
AL LT LV MK RO SI

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(30) Priority: 27.08.2001 JP 2001255685

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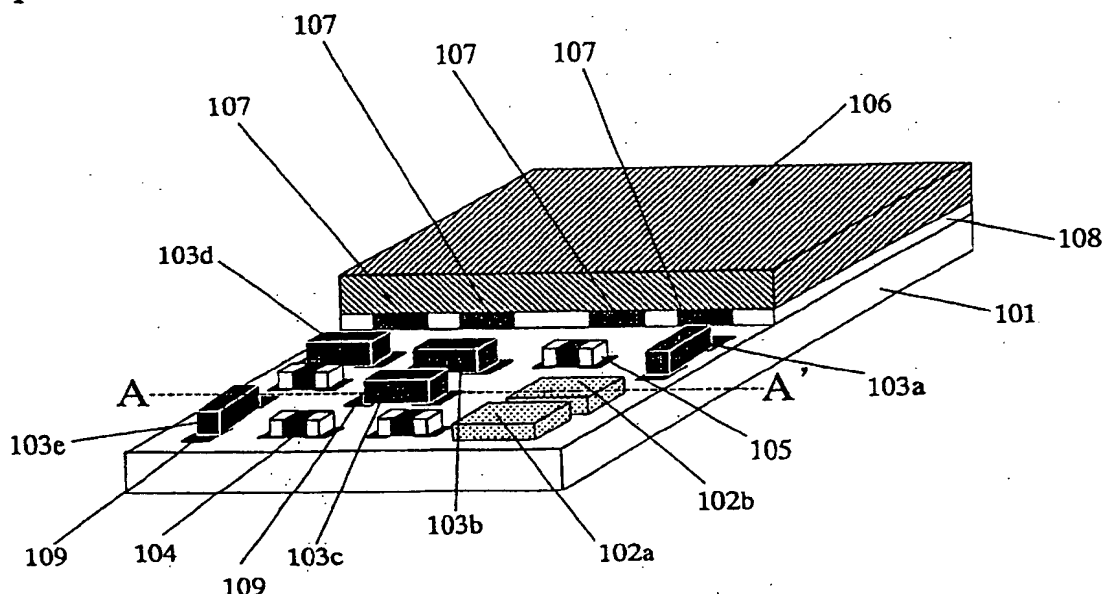
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(54) RF device and communication apparatus using the same

(57) An RF device, has a first substrate made of a material with a lower relative dielectric constant and having a high frequency circuit formed therein or on a surface thereof; and
a second substrate made of a material with a high-

er relative dielectric constant,
wherein at least a part of a filter is provided in, on a surface of or in the vicinity of the second substrate and connected to the high frequency circuit, and
the high frequency circuit is composed of an element other than the part of the filter.

Fig. 1





European Patent
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EUROPEAN SEARCH REPORT

Application Number
EP 02 01 9050

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Place of search THE HAGUE		Date of completion of the search 30 September 2003	Examiner Pastor Jiménez, J-V
<p>CATEGORY OF CITED DOCUMENTS</p> <p>X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document</p> <p>T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document</p>			

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